

TRANSMITTAL LETTER TO THE UNITED STATES
DESIGNATED/ELECTED OFFICE (DO/EO/US)
CONCERNING A FILING UNDER 35 U.S.C. 371

9847-0058-6X PCT

U.S. APPLICATION NO. (IF KNOWN, SEE 37 CFR

09/554912

INTERNATIONAL APPLICATION NO.

PCT/EP98/07740

INTERNATIONAL FILING DATE

NOVEMBER 30, 1998

PRIORITY DATE CLAIMED

NOVEMBER 28, 1997

TITLE OF INVENTION

MAGNETIC ENERGY STORAGE

APPLICANT(S) FOR DO/EO/US

Par HOLMBERG, et al.

Applicant herewith submits to the United States Designated/Elected Office (DO/EO/US) the following items and other information:

1. ☒ This is a **FIRST** submission of items concerning a filing under 35 U.S.C. 371.
1. ☐ This is a **SECOND** or **SUBSEQUENT** submission of items concerning a filing under 35 U.S.C. 371.
3. ☒ This is an express request to begin national examination procedures (35 U.S.C. 371(f)) at any time rather than delay examination until the expiration of the applicable time limit set in 35 U.S.C. 371(b) and PCT Articles 22 and 39(1).
4. ☒ A proper Demand for International Preliminary Examination was made by the 19th month from the earliest claimed priority date.
5. ☒ A copy of the International Application as filed (35 U.S.C. 371 (c) (2))
 - a. ☐ is transmitted herewith (required only if not transmitted by the International Bureau).
 - b. ☒ has been transmitted by the International Bureau.
 - c. ☐ is not required, as the application was filed in the United States Receiving Office (RO/US).
6. ☐ A translation of the International Application into English (35 U.S.C. 371(c)(2)).
7. ☒ A copy of the International Search Report (PCT/ISA/210).
8. ☒ Amendments to the claims of the International Application under PCT Article 19 (35 U.S.C. 371 (c)(3))
 - a. ☐ are transmitted herewith (required only if not transmitted by the International Bureau).
 - b. ☐ have been transmitted by the International Bureau.
 - c. ☐ have not been made; however, the time limit for making such amendments has NOT expired.
 - d. ☒ have not been made and will not be made.
9. ☐ A translation of the amendments to the claims under PCT Article 19 (35 U.S.C. 371(c)(3)).
10. ☐ An oath or declaration of the inventor(s) (35 U.S.C. 371 (c)(4)).
11. ☐ A copy of the International Preliminary Examination Report (PCT/IPEA/409).
12. ☐ A translation of the annexes to the International Preliminary Examination Report under PCT Article 36 (35 U.S.C. 371 (c)(5)).

Items 13 to 18 below concern document(s) or information included:

13. ☒ An Information Disclosure Statement under 37 CFR 1.97 and 1.98.
14. ☐ An assignment document for recording. A separate cover sheet in compliance with 37 CFR 3.28 and 3.31 is included.
15. ☒ A **FIRST** preliminary amendment.
A **SECOND** or **SUBSEQUENT** preliminary amendment.
16. ☒ A substitute specification.
17. ☐ A change of power of attorney and/or address letter.
18. ☐ Certificate of Mailing by Express Mail
19. ☒ Other items or information:

Request for Consideration of Documents Cited in International Search Report**Notice of Priority****Form PTO 1449****List of Related Cases****Marked-up Specification****Response to Petition Under 37 CFR 1.182**

U.S. APPLICATION NO. (IF KNOWN, SEE 37 CFR 1.52) <div style="font-size: 24pt; font-weight: bold; text-align: center;">097554912</div>	INTERNATIONAL APPLICATION NO. <div style="font-weight: bold; text-align: center;">PCT/EP98/07740</div>	ATTORNEY'S DOCKET NUMBER <div style="font-weight: bold; text-align: center;">9847-0058-6X PCT</div>
--	---	--

20. The following fees are submitted:

		CALCULATIONS	PTO USE ONLY
BASIC NATIONAL FEE (37 CFR 1.492 (a) (1) - (5)) :			
<input checked="" type="checkbox"/> Search Report has been prepared by the EPO or JPO	\$840.00		
<input type="checkbox"/> International preliminary examination fee paid to USPTO (37 CFR 1.482)	\$670.00		
<input type="checkbox"/> No international preliminary examination fee paid to USPTO (37 CFR 1.482) but international search fee paid to USPTO (37 CFR 1.445(a)(2))	\$760.00		
<input type="checkbox"/> Neither international preliminary examination fee (37 CFR 1.482) nor international search fee (37 CFR 1.445(a)(2)) paid to USPTO	\$970.00		
<input type="checkbox"/> International preliminary examination fee paid to USPTO (37 CFR 1.482) and all claims satisfied provisions of PCT Article 33(2)-(4)	\$96.00		
ENTER APPROPRIATE BASIC FEE AMOUNT =		\$840.00	
Surcharge of \$130.00 for furnishing the oath or declaration later than months from the earliest claimed priority date (37 CFR 1.492 (e)). <input type="checkbox"/> 20 <input checked="" type="checkbox"/> 30		\$130.00	
CLAIMS	NUMBER FILED	NUMBER EXTRA	RATE
Total claims	43 - 20 =	23	x \$18.00
Independent claims	3 - 3 =	0	x \$78.00
Multiple Dependent Claims (check if applicable) <input type="checkbox"/>			\$0.00
TOTAL OF ABOVE CALCULATIONS =			\$1,384.00
Reduction of 1/2 for filing by small entity, if applicable. Verified Small Entity Statement must also be filed (Note 37 CFR 1.9, 1.27, 1.28) (check if applicable). <input type="checkbox"/>			\$0.00
SUBTOTAL =			\$1,384.00
Processing fee of \$130.00 for furnishing the English translation later than months from the earliest claimed priority date (37 CFR 1.492 (f)). <input type="checkbox"/> 20 <input type="checkbox"/> 30			\$0.00
TOTAL NATIONAL FEE =			\$1,384.00
Fee for recording the enclosed assignment (37 CFR 1.21(h)). The assignment must be accompanied by an appropriate cover sheet (37 CFR 3.28, 3.31) (check if applicable). <input type="checkbox"/>			\$0.00
TOTAL FEES ENCLOSED =			\$1,384.00
			Amount to be refunded \$
			charged \$

☒ A check in the amount of **\$1,384.00** to cover the above fees is enclosed.

☐ Please charge my Deposit Account No. _____ in the amount of _____ to cover the above fees.
A duplicate copy of this sheet is enclosed.

☒ The Commissioner is hereby authorized to charge any fees which may be required, or credit any overpayment to Deposit Account No. **15-0030** A duplicate copy of this sheet is enclosed.

NOTE: Where an appropriate time limit under 37 CFR 1.494 or 1.495 has not been met, a petition to revive (37 CFR 1.137(a) or (b)) must be filed and granted to restore the application to pending status.

SEND ALL CORRESPONDENCE TO:

OBLON, SPIVAK, McCLELLAND, MAIER & NEUSTADT, P.C.
 Crystal Square Five, Fourth Floor
 1755 Jefferson Davis Highway
 Arlington, Virginia 22202
 703-413-3000

WILLIAM E. BEAUMONT
REGISTRATION NUMBER 30,996

SIGNATURE

Gregory J. Maier

NAME

25,599

REGISTRATION NUMBER

May 22, 2000

DATE

9847-0058-6XPCT
ENKEL 8359

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF: :
HOLMBERG, P., ET AL. : ATTN: APPLICATION DIVISION
SERIAL NO: NEW APPLICATION :
(BASED ON PCT EP98/07740)
FILED: HERewith :
FOR: MAGNETIC ENERGY STORAGE :

PRELIMINARY AMENDMENT

ASSISTANT COMMISSIONER OF PATENTS
WASHINGTON, DC 20231

Prior to examination on the merits, please amend the above-identified application as follows:

IN THE CLAIMS

Please cancel Claims 1-36 without prejudice or disclaimer and add Claims 37-79 as follows:

--37. An SMES device comprising:
a switch configured to short circuit a coil; and
said coil configured to be connected in series with a voltage source and wound from a
superconducting cable, said coil including
a superconductor maintained at cryogenic temperatures below a critical
temperature during use, and

an electrical insulation configured to surround said superconducting material,
wherein said electrical insulation including

- an inner layer of semiconducting material electrically connected to said superconductor,
- an outer layer of semiconducting material held at a controlled electric potential along a length of said outer layer of semiconducting material, and
- an intermediate layer of a solid electrically insulating material positioned between said inner layer of semiconducting material and said outer layer of semiconducting material.

38. The SMES device according to claim 37, further comprising:

a cryostat configured to enclose said coil and said switch.

39. The SMES device according to claim 37, wherein said superconductor comprises:

a high-temperature superconductor.

40. The SMES device according to claim 39, wherein said high-temperature superconductor comprises:

at least one layer of high-temperature superconducting material;

a cooler configured to cryogenically cool said at least one layer of high-temperature superconducting material below said critical temperature; and

a thermal insulator configured to surround said at least one layer of high-temperature superconducting material and said cooler.

41. The SMES device according to claim 40, wherein said cooler comprises:

a support tube through which a cryogenic cooling fluid is passed and about which said at least one layer of high-temperature superconducting material is wound as a tape in a helical layer.

42. The SMES device according to claim 40, wherein said cooler comprises:

a support tube through which a cryogenic cooling fluid is passed and about which said at least one layer of high-temperature superconducting material is wound as a plurality of conductors in a helical layer.

43. The SMES device according to claim 40, wherein said thermal insulator comprises:

an annular space under vacuum containing a thermal insulation.

44. The SMES device according to claim 37, wherein said outer layer of semiconducting material having a resistivity in an inclusive range from 1 through 1000 ohm-cm.

45. The SMES device according to claim 43, wherein said outer layer of semiconducting material having a resistivity in an inclusive range from 10 through 500 ohm-cm.

46. The SMES device according to claim 43, wherein said outer layer of semiconducting material having a resistivity in an inclusive range from 10 through 100 ohm-cm.

47. The SMES device according to claim 37, wherein said outer layer of semiconducting material having a resistance per axial unit length in an inclusive range from 5 through 50,000 ohm-m⁻¹.

48. The SMES device according to claim 37, wherein said outer layer of semiconducting material having a resistance per axial unit length in an inclusive range from 500 through 25,000 ohm-m⁻¹.

49. The SMES device according to claim 37, wherein said outer layer of semiconducting material having a resistance per axial unit length in an inclusive range from 2,500 through 5,000 ohm-m⁻¹.

50. The SMES device according to claim 37, wherein said outer layer of semiconducting material being contacted by a conductor at said controlled electric potential at a plurality of separated regions along said length of said outer layer of semiconducting material such that adjacent regions of said plurality of separated regions being sufficiently close together that a plurality of mid-point voltages between said adjacent regions being insufficient to cause a corona discharge to occur within said electrical insulator.

51. The SMES device according to claim 37, wherein said controlled electric potential being substantially an earth potential.

52. The SMES device according to claim 37, wherein said intermediate layer being in close mechanical contact with said inner layer of semiconducting material and said outer layer of semiconducting material.

53. The SMES device according to claim 37, wherein said intermediate layer being joined to said inner layer of semiconducting material and said outer layer of semiconducting material.

54. The SMES device according to claim 37, wherein a strength of adhesion between said intermediate layer and said inner layer of semiconducting material and said

outer layer of semiconducting material being greater than one tenth and less than ten times an intrinsic strength of said solid electrically insulating material of said intermediate layer.

55. The SMES device according to claim 53, wherein said intermediate layer, said inner layer of semiconducting material, and said outer layer of semiconducting material being joined together by extrusion.

56. The SMES device according to claim 55, wherein said intermediate layer, said inner layer of semiconducting material, and said outer layer of semiconducting material being applied together over said superconductor via a multi-layer extrusion die.

57. The SMES device according to claim 37, wherein:

said inner layer of semiconducting material including a first plastic material having a first plurality of electrically conductive particles dispersed therein; and

said outer layer of semiconducting material including a second plastic material having a second plurality of electrically conductive particles dispersed therein; and

said solid electrically insulating material of said intermediate layer including a third plastic material.

58. The SMES device according to claim 57, wherein said first plastic material, said second plastic material, and said third plastic material comprise:

at least one of an ethylene butyl acrylate copolymer rubber, an ethylene-propylene-diene monomer rubber, an ethylene-propylene copolymer rubber, a LDPE, a HDPE, a PP, a PB, a PMB, a XLPE, an EPR, and a silicone rubber.

59. The SMES device according to claim 57, wherein said first plastic material, said second plastic material, and said third plastic material having a substantially identical coefficient of thermal expansion.

60. The SMES device according to claim 57, wherein said first plastic material, said second plastic material, and said third plastic material being a substantially identical material.

61. The SMES device according to claim 37, wherein said SMES device being connected to a high voltage source and forming an electric power transmission system.

62. A high voltage system, comprising:

an SMES device having a superconductor insulated against a high voltage by an electric insulation system arranged concentrically around said superconductor.

63. The high voltage system according to claim 62, wherein said high voltage system further comprises:

a high voltage network directly connected to said SMES device without an intermediate transformer.

64. The high voltage system according to claim 63, wherein said high voltage network comprises a high voltage DC network.

65. The high voltage system according to claim 64, wherein said high voltage DC network being configured to operate at a voltage exceeding 10 kV.

66. The high voltage system according to claim 63, further comprising:

a converter configured to couple said SMES device to a high voltage AC network.

67. The high voltage system according to claim 64, further comprising:

a plurality of AC networks connected via said DC network and said SMES device, wherein said DC network being connected to said plurality of AC networks so that said SMES device provides said plurality of AC networks with power.

68. The high voltage system according to claim 62, wherein said SMES device comprises:

a coil.

69. The high voltage system according to claim 62, wherein said SMES device comprises:

a cable without turns.

70. The high voltage system according to claim 66, wherein said SMES forming a part of a bipolar DC link.

71. The high voltage system according to claim 62, wherein said insulation system comprises:

a first integral semiconducting part configured to form an inner layer in electric contact with said superconductor;

a second integral semiconducting part configured to form an outer layer around an insulating integral third part; and

said insulating integral third part between said first integral semiconducting part and said second integral semiconducting part;

wherein said insulation system being extruded around said superconductor.

72. The high voltage system according to claim 62, wherein said insulation system comprises:

an all-synthetic semiconducting film wound in an overlapping layer around said superconductor with an inner part of said all-synthetic film in electric contact with said superconductor;

an electrically insulating intermediate part; and

an outer semiconducting part surrounding said electrically insulating intermediate part.

73. The high voltage system according to claim 62, wherein said insulation system comprises:

at least one of a cellulose-based, synthetic paper and a non-woven fibre material being co-lapped with a synthetic film and including

an inner semiconducting part in electric contact with said superconductor,

an electrically insulating intermediate part, and

an outer semiconducting part around said electrically insulating intermediate part.

74. The high voltage system according to claim 62, wherein said insulation system comprises:

at least one of a cellulose-based, synthetic paper and a non-woven fibre material being laminated with a synthetic film and including

an inner semiconducting part in electric contact with said superconductor,

an electrically insulating intermediate part, and

an outer semiconducting part around said electrically insulating intermediate part.

75. The high voltage system according to claim 71, further comprising:

a cooling medium configured to cool said superconductor through flow within said superconductor.

76. The high voltage system according to claim 72, further comprising:

a cooling medium configured to cool said superconductor through flow within said superconductor.

77. The high voltage system according to claim 71, further comprising:

a cooling medium configured to cool said superconductor arranged outside of said superconductor.

78. The high voltage system according to claim 72, further comprising:
a cooling medium configured to cool said superconductor arranged outside of said
superconductor.

79. An SMES device comprising:
a switch configured to short circuit a coil; and
said coil configured to be connected in series with a voltage source and wound from a
superconducting cable, said coil including

means for superconducting maintained at cryogenic temperatures below a
critical temperature during use, and

means for electrically insulating said means for superconducting, including
an inner layer of a semiconducting material electrically connected to
said means for superconducting,

an outer layer of semiconducting material held at a controlled electric
potential along a length thereof, and

an intermediate layer of a solid electrical insulation positioned between
said inner layer and said outer layer.--

IN THE ABSTRACT OF THE DISCLOSURE

After the last page of the Specification, please insert the following:

ABSTRACT OF THE DISCLOSURE

--

A superconducting magnetic energy storage (SMES) device and a high voltage system containing such a device where the electrical insulation of the superconductor is formed by an inner layer of semiconducting material electrically connected to the superconductor, an outer layer of semiconducting material at a controlled electric potential, and an intermediate layer of solid electrically insulating material positioned between the inner and outer layers. The SMES can thus be coupled directly to a high voltage network, allowing load-following to be performed on a transmission or distribution network.--

REMARKS

Favorable consideration of this Application as presently amended is respectfully requested.

Claims 37-79 are active in the present Application; Claims 1-36 having been canceled and Claims 37-79 added by way of the present Preliminary Amendment. The new claims have been added to draft the canceled claims in a manner consistent with U.S. practice. It is therefore believed that no issues of new matter have been raised.

Entry of the enclosed substitute specification is respectfully requested. Because several amendments have been made to the specification, consistent with U.S. patent drafting practice, a marked-up copy of the original application is filed herewith. To the extent that any of the changes made by the substitute specification are deemed to be substantively inconsistent with the originally filed specification, these changes should be construed as typographical errors and the language included in the originally-filed PCT application should be construed as containing the controlling language.

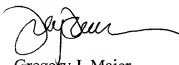
The present document is one of a set of patent applications containing related technology as was discussed in "response to petition under 37 C.F.R. §1.182 seeking special treatment relating to an electronic search tool, and decision on petition under 37 C.F.R. §1.183 seeking waiver of requirements under 37 C.F.R. §1.98," filed in the holding application (U.S. Patent Application No. 09/147,325). Consistent with this decision, a copy of the decision is filed herewith. Also, an Information Disclosure Statement is filed herewith including a PTO Form 1449 with references that are included as part of the specially-created official digest in class 174. It is believed that submission of these materials and the reference

to the holding application (Serial No. 09/147,325) is sufficient for the present Examiner to consider the references in the holding application, consistent with the decision.

Accordingly, examination on the merits of Claims 37-79 is believed to be in order, and an early and favorable action is respectfully requested.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.



Gregory J. Maier
Registration No. 25,599
Bradley D. Lytle
Registration No. 40,073
Attorneys of Record

Crystal Square Five - Fourth Floor
1755 Jefferson Davis Highway
Arlington, VA 22202
(703) 413-3000
Fax #: (703) 413-2220
GJM/BDL/JFC:jms
E:\atty\jfc\9847\0058\98470058-6xpct.am.wpd

WILLIAM E. BEAUMONT
REGISTRATION NUMBER 30,996

SUBSTITUTE SPECIFICATION

9847-0058-6XPCT

ENKEL 8359

TITLE OF THE INVENTION

MAGNETIC ENERGY STORAGE

CROSS REFERENCE TO RELATED PATENT DOCUMENTS

The present document is based on published international patent application No. WO 99/28921, the entire contents of which being incorporated herein by reference.

BACKGROUND OF THE INVENTIONField of the Invention:

This invention relates to a superconducting magnetic energy storage (SMES) device including a coil for connection in series with a voltage source, e.g. a DC voltage source, and wound from a superconducting cable having a superconductor which, in use, is maintained at cryogenic temperatures below its critical temperature (T_c) and which is surrounded by electrical insulation, and a switch for short-circuiting the coil. Although the invention primarily relates to high-temperature superconducting cables, the invention is also applicable to low-temperature superconducting cables because of the high magnetic field in magnetic energy storage.

Discussion of the Background:

The concept of superconducting magnetic energy storage (SMES) is well known. The principle of SMES is that energy is stored as magnetic energy in a coil having an inductance L , the amount of energy stored being given by $\frac{1}{2}LI^2$, where I is the DC current.

The inductance L of a coil is given through the well-known relationship:

$$L = (\mu_0 \mu_r N^2 A) / l$$

where $\mu_0 = 4\pi \times 10^{-7}$ As/Vm, μ_r is the permeability of material in the magnetic circuit of a solenoid (which is 1 for air and around 10000 or higher for oriented laminated quality steel, provided the magnetic flux density B is sufficiently low), N is the number of windings, A is the cross-sectional area and l the length of the coil.

Since the magnetic energy E to be stored in a SMES device is $E = \frac{1}{2}LI^2$, it is evident that both current and inductance should be maximized. The maximum current is given through the properties of a superconductor at given temperature, magnetic field, and current density.

The inductance could be maximized by utilising a magnetic material in the magnetic circuit having a high permeability. Unfortunately, there are no known materials having a high permeability at high flux densities. In fact, at B around 2 Tesla, even the best materials go into saturation and, in addition, core losses (hysteresis and eddy) increase drastically in the saturation region. If the magnetic moments of a material are perfectly aligned, it is theoretically possible to reach a maximum flux density of 2.12 Tesla for iron. Due to the high currents of superconductors, the flux densities are also high, in fact densities of 5 T and more are not uncommon. Thus magnetic material should not be included in the magnetic circuit, at least not in regions of high B . In general, μ_r is then equal to one.

The inductance can also be increased by choosing a high number of windings N . If a solenoid is wound, then the winding density, that is the number of windings per unit length, is determined by the cross-sectional area of the conductor and its insulation.

The ratio of cross-sectional area to length is also an important parameter for the inductance. The aim should be to achieve a large cross-section and a short coil length. Thus pancake or disk windings are often designed as a preferred coil for achieving high inductances.

SMES devices have a high efficiency and high energy density compared with competing systems for storing energy. SMES devices can have a rapid response to demands of storing or discharging. In addition, SEES devices can be used not only for load-levelling but also for load-following, for spinning reverse, for transient stabilization, and for synchronous resonance damping. SMES can provide not only energy savings but also a larger freedom of power system operation.

Normally SMES devices are built for storing energy up to about 1 MW, but there is a demand for SMES devices with higher energy storage capability. Current solutions for larger SMES devices involve oversizing of equipment and the usage of multiple feeders connected to different transmission systems.

Conventional SMES devices operate with high current sources at low voltages. When used in an AC power system, an AC/DC converter can be used for converting the power to and from the SMES device. Operation of SMES devices connected to power networks will include a transformer.

A SMES device is normally built as a coil. In order to maximize the storage capability, the inductance should be as high as possible. Therefore, the superconductor is wound into a pancake, for example a 4 T background coil for SMES as described in "Design and construction of the 4 T background coil for the navy SMES cable test apparatus", IEEE Transactions on Applied Superconductivity, Vol 7, No 2, June 1997. The SMES devices are normally connected to voltages of up to about 500 V and currents of around 1000 A.

A large SMES device for 30MW is described in IEEE Transactions on Applied Superconductivity, Vol 7, No. 2, June 1997 in the article "Quench Protection and Stagnant Normal Zones in a Large Cryostable SMES," and involves a coil assembled from a multiple double pancake structure. The application of this SMES device requires a high power discharge and the operating voltage is desired to be up to 3.4 kV.

Another method of storing magnetic energy can be by winding the conductor directly as a solenoid. An example of a test coil is described in "Design, manufacturing and cold test of superconducting coil and its cryostat for SMES applications", IEEE Transactions on Applied Superconductivity, Vol 7, No. 2, June 1997, where a solenoid is formed from a NbTi conductor with 4500 turns, 30 layers, and an inner winding radius of 120 mm.

SUMMARY OF THE INVENTION

An aim of the present invention is to have a high voltage system including a SMES device, where superconducting conductors of the SMES device are insulated against high voltage and the insulation is concentric around the conductors.

According to one aspect of the present invention there is provided a SMES device of the kind referred to, characterized in that the said electrical insulation includes an inner layer of semiconducting material electrically connected to said superconductor, an outer layer of semiconducting material at a controlled electric potential, e.g. earth potential, along its length and an intermediate layer of solid electrically insulating material positioned between said inner and outer layers.

In this specification the term "semiconducting material" indicates a material which has a considerably lower conductivity than an electrical conductor but which does not have such a low conductivity that it is an electrical insulator. Suitably, but not exclusively, a "semiconducting material" should have a volume resistivity of from $1 \cdot 10^5 \Omega \cdot \text{cm}$ preferably from $1 \cdot 10^3 \Omega \cdot \text{cm}$, more preferably $10 \cdot 500 \Omega \cdot \text{cm}$, and most preferably $10 \cdot 100 \Omega \cdot \text{cm}$, typically $20 \Omega \cdot \text{cm}$.

The present invention is not limited to high temperature superconductivity. Due to the high magnetic field in magnetic energy storage, low temperature superconductors are still attractive, even though they require cryostats operating between 1-15 K, depending on the type of low temperature superconductor utilized. Well-known examples are based on niobium, such as NbTi, Nb₃Sn and Nb₃Al.

Other examples are V₃Ga and Nb₃Ge. The most common superconductor used is NbTi which can be utilized in magnetic field densities up to approximately 9 T at 4.2 K (or 11 T at 1.8 K). For higher field densities, NbTi cannot be used and is replaced by Nb₃Sn.

An SMES device according to the invention is made from cable-like conductors which can be manufactured according to conventional principles of cable manufacturing. The insulation is such that it can withstand high voltages in the range of 1 kV and upwards to the voltages used for high voltage DC current transmission.

The invention allows a high voltage system that includes an SMES device. The SMES device can be coupled to a high voltage network. This allows load-following to be performed on a transmission or distribution network and not only for a specific use with lower voltages as is the case with the SMES devices of today. This opens up the possibility of using a SMES for storing energy to smooth load variations in a high voltage network on, for example, a day-night basis or an east-west basis. Also, a SMES device operating at a high

voltage can be capable of injecting large amounts of energy into a system in a short time, that is injecting a large amount of real power, which will allow for good control of the system.

The present invention provides a high voltage system that includes an SMES system which can be directly coupled to a high voltage of up to 800 kV and even above without the need to transform the voltage down. This can be achieved by insulating the superconductor with an insulation system that can withstand high voltages. Such insulation systems are known, for example, from high voltage DC transmission systems.

A specific advantage of the present invention is that, since the SMES device operates at high voltage, the current can be reduced for a given power density. Thus, by way of example only, for a conventional SMES device operating at 20 kV, a similarly powered SMES device according to the invention can operate at about 150 kV resulting in a reduction of the current of about 7.5 times. Since the magnetic force in the cable is proportional to current x magnetic flux density (B), the magnetic force is effectively reduced about 7.5 times. Furthermore, the amount of semiconductor saved will, in this example, amount to approximately 7.5 times. Similarly, the cooling losses will be essentially reduced. All these factors improve the economic attractiveness of the SMES device.

A further advantage with an SMES device operating at high voltages is that charging and discharging can be rapid. It is normally very time-consuming to charge at least larger SMES devices, and by connecting the SMES device to a high voltage the charging time can be substantially reduced. Also, the power that can be delivered from the SMES device is increased by increasing the voltage across the SMES device.

Another advantage is that an SMES device can be installed close to a large power generating unit, such as a nuclear power station. During a rapid close-down of a nuclear power station, there are great strains on the network. These can be effectively smoothed by a high voltage SMES device that is able to inject the corresponding power into the system and then allow for a slow ramp down of the power.

Another advantage of a high voltage SMES device is that there is no need for a transformer to be provided for transforming power to and from the SMES device. The SMES device can be directly coupled to a transmission or distribution network without intermediate step-up transformers. The elimination of transformers in the system leads to higher efficiency of the system. The performance of the SMES system will be greatly improved by being able

to connect the SMES device directly to a power network and by the increased efficiency that is created by the reduction of the number of components in the system.

Another advantage is that the SMES device is wholly electrically insulated in such a way that there is no electric field outside the superconducting cable. This facilitates the design of the mechanical structure holding the cables. It is possible to scale up the SMES device with fewer problems with the mechanical stability of the SMES device.

Another advantage of an SMES device with high voltage insulation is that discharges that normally occur in the electric system are prevented by the insulation system and the risk of bubble formation in the cooling medium is therefore reduced.

By connecting the coil directly to a high voltage DC source, e.g. to a high voltage AC/DC converter, charging and discharging of the coil is simplified. In particular, in an AC power transmission system, the need to transform the AC voltage down prior to connection to an AC/DC converter is eliminated. By holding the semiconducting outer layer at a controlled electric potential, e.g. ground or earth potential along its length, e.g. at spaced apart intervals along its length, the electric field generated by the superconductor is contained within the electrical insulation.

Conveniently the coil and switch are enclosed within a cryostat for maintaining the temperature of the superconductor below its critical temperature (T_c). Alternatively, or in addition, the superconductor may be internally cooled by a cryogenic fluid, e.g. liquid nitrogen, and externally thermally insulated. For example, thermal insulation may conveniently be provided between the superconductor and the surrounding electrical insulation. In some cases, the electrical insulation can also function as thermal insulation.

By only using, for the intermediate layer, materials which can be manufactured with few, if any, defects and by providing the intermediate layer with the spaced apart inner and outer layers of semiconducting material having similar thermal properties, thermal and electrical loads within the insulation are reduced. In particular, the insulating intermediate layer and the semiconducting inner and outer layers should have at least substantially the same coefficients of thermal expansion (α) so that defects caused by different thermal expansions when the layers are subjected to heating or cooling will not arise. Ideally, the electrical insulation is of substantially unitary construction. The layers of the insulation may be in close mechanical contact but are preferably joined or united together. Preferably, for

example, the radially adjacent layers will be extruded together around the superconductor. The superconducting cable is flexible at normal ambient temperatures and thus can be bent or flexed into its desired winding shape prior to operation at cryogenic temperatures.

Conveniently the electrically insulating intermediate layer is formed from a solid thermoplastic material, such as low or high density polyethylene (LDPE or HDPE), polypropylene (PP), polybutylene (PB), polymethylpentene (PMP), ethylene (ethyl) acrylate copolymer, cross-linked materials, such as cross-linked polyethylene (XLPE), or rubber insulation, such as ethylene propylene rubber (EPR) or silicone rubber. The semiconducting inner and outer layers may include a similar material to the intermediate layer but with conducting particles, such as carbon black, soot, or metallic particles, embedded therein. Generally, it has been found that a particular insulating material, such as EPR, has similar mechanical properties when containing no, or some, carbon particles.

The screens of semiconducting inner and outer layers form substantially equipotential surfaces on the inside and outside of the insulating intermediate layer so that the electric field, in the case of concentric semiconducting and insulating layers, is substantially radial and confined within the intermediate layer. In particular, the semiconducting inner layer is arranged to be in electrical contact with, and to be at the same potential as, the superconductor that it surrounds. The semiconducting outer layer is designed to act as a screen to prevent losses caused by induced voltages. Induced voltages could be reduced by increasing the resistance of the outer layer. Since the thickness of the semiconducting layer cannot be reduced below a certain minimum thickness, the resistance can only be reduced by selecting a material for the layer having a higher resistivity. However, if the resistivity of the semiconducting outer layer is too great the voltage potential between adjacent spaced apart points at a controlled, e.g. earth, potential will become sufficiently high as to risk the occurrence of corona discharge with consequent erosion of the insulating and semiconducting layers. The semiconducting outer layer is therefore a compromise between a conductor having low resistance and high induced voltage losses but which is easily connected to a controlled electric potential, typically earth or ground potential, and an insulator which has high resistance with low induced voltage losses but which needs to be connected to the controlled electric potential along its length. Thus the resistivity ρ_s of the semiconducting outer layer should be within the range $\rho_{\min} < \rho_s < \rho_{\max}$, where ρ_{\min} is determined by permissible

power loss caused by eddy current losses and resistive losses caused by voltages induced by magnetic flux and ρ_{\max} is determined by the requirement for no corona or glow discharge.

If the semiconducting outer layer is earthed, or connected to some other controlled electric potential, at spaced apart intervals along its length, there is no need for an outer metal shield and protective sheath to surround semiconducting outer layer. The diameter of the cable is thus reduced allowing more turns to be provided for a given size of winding.

The electrical insulation can be extruded over the superconductor or a lapped concept can be used. This can include both the semiconducting layers and the electrically insulating layer. An insulation can be made of an all-synthetic film with inner and outer semiconducting layers made of a polymeric thin film of, for example, PP, PET, LDPE or HDPE with embedded conducting particles, such as carbon black or metallic particles.

For the lapped concept, a sufficiently thin film will have butt gaps smaller than the so-called Paschen minima, thus rendering liquid impregnation unnecessary. A dry, wound multilayer thin film insulation has also good thermal properties and can be combined with a superconducting pipe as an electric conductor and have coolant, such as liquid nitrogen, pumped through the pipe.

Another example of electrical insulation is similar to a conventional cellulose based cable, where a thin cellulose based or synthetic paper or non-woven material is lap wound around a conductor. In this case the semiconducting layers can be made of cellulose paper or nonwoven material made from fibres of insulating material and with conducting particles embedded. The insulating layer can be made from the same base material or another material can be used.

Another example is obtained by combining film and fibrous insulating material, either as a laminate or as co-lapped. An example of this insulation system is the commercially available so-called paper polypropylene laminate, PPLP, but several other combinations of film and fibrous parts are possible. In these systems various impregnations such as mineral oil or liquid nitrogen can be used.

The superconductor may be formed from low temperature semiconductors, but most preferably is formed from high-temperature superconducting (HTS) materials, for example HTS wires or tape helically wound on an inner tube. The HTS tape conveniently is silver-sheathed BSCCO-2212 or BSCCO-2223 (where the numerals indicate the number of atoms

of each element in the $[Bi, Pb]_2Sr_2Ca_2Cu_3O_x$ molecule) and hereinafter such HTS tapes will be referred to as "BSCCO tape(s)". BSCCO tapes are made by encasing fine filaments of the oxide superconductor in a silver or silver oxide matrix by a powder-in-tube (PIT) draw, roll, sinter and roll process. Alternatively the tapes may be formed by a surface coating process. In either case the oxide is melted and resolidified as a final process step. Other HTS tapes, such as $TiBaCaCuO$ (TBCCO-1223) and $YBaCuO$ (YBCO-123) have been made by various surface coating or surface deposition techniques. Ideally an HTS wire should have a current density beyond $j_c \sim 10^5 \text{ Acm}^{-2}$ at operation temperatures from 65 K, but preferably above 77 K. The filling factor of ITS in the matrix needs to be high so that the engineering current density $j_e \geq 10^4 \text{ Acm}^{-2}$. j_c should not drastically decrease with applied fields within the Tesla range. The helically wound HTS tape is cooled to below the critical temperature T_c of the HTS by a cooling fluid, preferably liquid nitrogen, passing through the inner support tube.

A cryostat layer may be arranged around the helically wound HTS tape to thermally insulate the cooled HTS tape from the electrically insulating material. Alternatively, however, the cryostat may be dispensed with. In this latter case, the electrically insulating material may be applied directly over the superconductor. Alternatively, a space may be provided between the superconductor and the surrounding insulating material, the space either being a void space or a space filled with compressible material, such as a highly compressible foamed material. The space reduces expansion/contraction forces on the insulation system during heating from/cooling to cryogenic temperatures. If the space is filled with compressible material, the latter can be made semiconducting to ensure electrical contact between the semiconducting inner layer and the superconductor.

Other designs of superconductors are possible, the invention being directed to transformer windings, formed from superconducting cables of any suitable design having a surrounding electrical insulation of the type described above. For example other types of superconductors may include, in addition to internally cooled HTS material, externally cooled HTS material or externally and internally cooled HTS material. In the latter type of HTS cable, two concentric HTS conductors separated by cryogenic insulation and cooled by liquid nitrogen are used to transmit electricity. The outer conductor acts as the return path and both HTS conductors may be formed of one or many layers of HTS tape for carrying the required current. The inner conductor may include HTS tape wound on a tubular support through

which liquid nitrogen is passed. The outer conductor is cooled externally by liquid nitrogen and the whole assembly may be surrounded by a thermally insulating cryostat.

According to another aspect of the present invention there is provided an electric power transmission system characterized in that an SMES device according to said one aspect is connected to a high voltage source, preferably a high voltage DC source.

The SMES device may be in the form of a cable and preferably a cable with high inductance. The electrical insulation of the cable can be made of conductor tape or wire with several layers where all layers are wound in the same direction, instead of as conventionally winding the layers in opposite direction in order to compensate for the inductance. Such cable with an extruded insulation system could be directly incorporated into a transmission line, for example as one line of a bipolar DC system.

It is also possible to use such cable to build up a solenoid with high inductance.

The invention as herein described can also be used with conventional low-temperature superconducting materials and with coolants such as liquid helium.

It is also possible to use the invention with an AC source. The losses are larger for an AC SMES device but if the losses are acceptable for the system to be designed, the principle of the invention is applicable.

BRIEF DESCRIPTION OF THE DRAWINGS

Embodiments of the invention will now be described, by way of example only, with particular reference to the accompanying drawings, in which:

Figure 1 is a circuit diagram of a SMES device according to the present invention;

Figure 2 is a schematic sectional view, on an enlarged scale, through part of one embodiment of a high-temperature superconducting cable from which the coil of the SMES device of Figure 1 is wound;

Figure 3 is a schematic sectional view, on an enlarged scale, of another embodiment of high temperature superconducting cable from which the coil of the SMES device of Figure 1 can be wound;

Figure 4 is a schematic view of two high voltage AC networks coupled together via a high voltage DC network and incorporating an SMES device on the DC side;

Figure 5 is a schematic view of an SMES incorporated in a high voltage DC network;
and

Figure 6 is a schematic view of two convertor stations with voltage source converters
and combined with a high voltage bipolar DC link.

DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS

Figure 1 shows a coil 1 having an inductance L formed of high-temperature (T_c)
superconducting (HTS) cable 12 (see Figure 2) which is connected with a high DC voltage
source 2, e.g. the DC side of a high voltage AC/DC converter connected to an AC power
transmission line. A switch 3 is connected in parallel with the high DC voltage source 2 and
is operable to short-circuit the coil 1.

When the coil 1 is connected to the dc voltage source 2, a DC current I flows and
charges the coil. Due to the high current density of the superconducting cable and its
virtually zero resistance, energy is simply stored by closing the switch 3 and short-circuiting
the coil. The energy in the coil is stored as magnetic energy having a value of $\frac{1}{2}LI^2$. The coil
1 is thus able to store electrical energy and to provide electrical power at a fast rate when
required at times of peak consumption.

The superconducting cable 12 from which the coil 1 is formed includes an inner
tubular support 13, e.g. of copper or a highly resistive metal, such as copper-nickel alloy, on
which is helically wound elongate HTS material, for example BSCCO tape or the like, to form
a superconducting layer 14 around the tubular support 13. A cryostat 15, arranged outside the
superconducting layer, includes two spaced apart flexible corrugated metal tubes 16 and 17.
The space between the tubes 16 and 17 is maintained under vacuum and contains thermal
superinsulation 18. Liquid nitrogen, or other cooling fluid, is passed along the tubular
support 13 to cool the surrounding superconducting layer 14 to below its critical
superconducting temperature T_c . The tubular support 13, superconducting layer 14 and
cryostat 15 together constitute the superconductor of the cable 12.

Solid electrical insulation, e.g. of plastic material, is arranged outside the
superconductor. The electrical insulation includes an inner semiconducting layer 20, an outer
semiconducting layer 21, and, sandwiched between these semiconducting layers, an
insulating layer 22. The layers 20-22 preferably are formed from thermoplastic materials

providing a substantially unitary construction. The layers may be in close mechanical contact with each other but are preferably solidly connected to each other at their interfaces.

Conveniently, these thermoplastic materials have similar coefficients of thermal expansion and are preferably extruded together around the inner superconductor. The electrical insulation conveniently has an electric field stress of no more than 0.2 kV/mm.

By way of example only, the solid insulating layer 22 may be formed from cross-linked polyethylene (XLPE). Alternatively, however, the solid insulating layer may be formed from other cross-linked materials, low density polyethylene (LDPE), high density polyethylene (HDPE), polypropylene (PP), polymethylpentene (PMP), ethylene (ethyl) acrylate copolymer, or rubber insulation, such as ethylene propylene rubber (EPR), ethylene-propylene-diene monomer (EPDM), or silicone rubber. The semiconducting material of the inner and outer layers 20 and 21 may be formed from, for example, a base polymer of the same material as the solid insulating layer 22 and highly electrically conductive particles, e.g. particles of carbon black or metallic particles, embedded in the base polymer. The volume resistivity of these semiconducting layers, typically about 20 ohm cm, may be adjusted as required by varying the type and proportion of carbon black added to the base polymer. The following gives an example of the way in which resistivity can be varied using different types and quantities of carbon black.

<u>Base Polymer</u>	<u>Carbon Black Type</u>	<u>Carbon Black Quantity (%)</u>	<u>Volume Resistivity $\Omega \cdot \text{cm}$</u>
Ethylene vinyl acetate copolymer/nitrite rubber	EC carbon black	-15	350-400
-"	P-carbon black	-37	70-10
-"	Extra conducting carbon black, type I	-35	40-50
-"	Extra conducting carbon black, type II	-33	30-60
Butyl grafted polyethylene	-"	-25	7-10
Ethylene butyl acrylate copolymer	Acetylene carbon black	-35	40-50
-"	P carbon black	-38	5-10
Ethylene propene rubber	Extra conducting carbon black	-35	200-400

The outer semiconductive layer 21 is connected to a desired controlled electric potential, e.g. earth potential, at spaced apart regions along its length, the specific spacing apart of adjacent controlled potential or earthing points being dependent on the resistivity of the layer 21.

The semiconducting layer 21 acts as a static shield and by controlling the electric potential of the outer layer, e.g. to earth potential, it is ensured that the electric field of the superconducting cable is retained within the solid insulation between the semiconducting layers 20 and 21. Losses caused by induced voltages in the layer 21 are reduced by increasing the resistance of the layer 21. However, since the layer 21 must be at least of a certain minimum thickness, e.g. no less than 0.8 mm, the resistance can only be increased by selecting the material of the layer to have a relatively high resistivity. The resistivity cannot be increased too much, however, else the voltage of the layer 21 mid-way between two adjacent earthing points will be too high with the associated risk of corona discharges occurring.

Instead of, or in addition to, internally cryogenically cooling the HTS cable 12, the coil 1 and switch 3 may be enclosed within a cryostat 6 (shown schematically in dashed lines in Figure 1) for keeping the coil 1 at temperatures below the critical temperature of the superconductor. In this case, the thermally insulating cryostat 15 need not be included in the HTS cable described above with reference to Figure 2. Figure 3 shows a typical design of cable having no cryostat 15. In this case, the electrical insulation, provided by the layers 20-22, is extruded directly over the superconducting layer 14 wound on the tubular support 13. Although not shown, an annular gap may be provided between the electric insulation and the layer 14 to cater for the differences in thermal expansion/contraction of the electrical insulation and the layer 14. This annular gap could be a void space or could be filled with compressible material, such as highly compressible foam material. If such an annular gap is provided, the semiconducting inner layer 20 is preferably placed in electrical contact with the superconducting layer 14. For example, if the compressible foam material is included in the annular gap, the foam material may be made semiconducting.

Figure 4 shows a high voltage system including two high voltage AC networks, N1 and N2, T1Y and T2Y are converter transformers in Y/Y coupling and T1D and T2D are converter transformers in Y/D coupling. SCR11, SCR12, SCR21 and SCR22 are series-connected 6-pulse line-commutated bridge-connected converters. The converters SCR11 and SCR12 are linked with the converters SCR21 and SCR22 via a DC link DCL which includes an energy storage device in the form of a superconducting magnetic storage device SMES.

The voltage across the converters SCR11 and SCR12 is U_1 and the voltage across converters SCR21 and SCR22 is U_2 . U_1 and U_2 are each controlled in a conventional manner by control equipment (not shown) connected with its respective converter. The current I_d runs through the DC link DCL and the device SMES.

In the system shown in Figure 4, $U_1 - U_2 = L \cdot di/dt$, which indicates that the charging and discharging of the device SMES can be controlled by the control angles of the converters. One or both converters can charge or discharge the SMES. By controlling $U_1=U_2$, the content of energy of the SMES can be unaffected.

Figure 5 shows the same basic high voltage system as Figure 4. In Figure 5, however, the superconducting magnetic energy storage device SMES is used as a storage device for the ac network N1 and is charged via the converters SCR11 and SCR12, with switch S1 closed

and switch S2 open. During charging of the device SMES, the current through the coil can be measured and charging continues until a nominal value is reached. When the SMES is fully charged, S1 opens and S2 closes. For feeding the network N1, for example in the case of a power loss on the network, S1 closes and S2 is opened.

In the Figure 5 system, the superconducting magnetic energy storage device SMES is part of a high voltage DC transmission system with a DC link. A pole control device, PCM, is needed when providing the network N2 with power.

Figure 6 shows a high voltage system having two voltage-controlled converters VSC1 and VSC2, which are connected via a DC link in the form of a double cable TC. The DC link is bipolar in that the capacitors C11 and C12 and the capacitors C21 and C22 are respectively connected to ground at their connecting point. A superconducting magnetic energy storage device SMES is arranged at one pole of the converter VSC1. It is also possible to arrange the superconducting magnetic energy storage device in the form of a cable as one part of the bipolar dc link.

Although the invention has been described with specific reference to an SMES device having a coil for connection in series with a DC voltage source, the invention is also intended to embrace connection of the coil to an AC voltage source.

The term "high voltage" used in this specification is intended to mean up to 800 kV or even higher. An SMES device may be connected to such high voltage networks and at high powers of up to 1000 MVA. At high voltages, partial discharges, or PD, constitute a serious problem for known insulation systems. If cavities or pores are present in the insulation, internal corona discharges may arise whereby the insulating material is gradually degraded eventually leading to breakdown of the insulation. The electric load on the electrical insulation of the superconductor of an SMES device according to the present invention is reduced by ensuring that the inner portion of the electrical insulation is at substantially the same electric potential as the superconductor and that the outer portion of the electrical insulation is at a controlled potential. Thus the electric field is distributed substantially uniformly over the thickness of the electrically insulating portion of the insulation between the inner and outer portions. By having materials for the electrical insulation with similar thermal properties and with few defects in the layers or portions, the possibility of PD is reduced.

An additional advantage of the present invention is that, since the SMES device operates at high voltage, the current can be reduced for a given power density. Thus for a conventional SMES device operating at 20 kV, a similarly powered SMES device according to the invention can operate at about 150 kV resulting in a reduction of the current of about 7.5 times. Since the magnetic force in the cable is proportional to current x magnetic flux density (B), the magnetic force is effectively reduced about 7.5 times. Furthermore, the amount of semiconductor saved will, in this example, amount to approximately 7.5 times. Similarly, the cooling losses will be essentially reduced. All these factors improve the economic attractiveness of the SMES device.

The present invention is not limited to high temperature superconductivity. Due to the high magnetic field in magnetic energy storage, low temperature superconductors are still attractive, even though they require cryostats operating between 1-15 K, depending on the type of low temperature superconductor utilized. Well-known examples are based on niobium, such as NbTi, Nb₃Sn and Nb₃Al. Other examples are V₃Ga and Nb₃Ge. The most common superconductor used is NbTi which can be utilized in magnetic field densities up to approximately 9 T at 4.2 K (or 11 T at 1.8 K). For higher field densities, NbTi cannot be used and is replaced by Nb₃Sn.

CLAIMS:

1. An SMES device comprising a coil (1) for connection in series with a voltage source (2), e.g. a dc voltage source, and wound from a superconducting cable (12) having superconducting means (14) which, in use, is maintained at cryogenic temperatures below its critical temperature (T_c) and which is surrounded by electrical insulation (20-22), and switch means (3) for shortcircuiting the coil (1), characterized in that the said electrical insulation comprises an inner layer (20) of semiconducting material electrically connected to said superconducting means, an outer layer (21) of semiconducting material at a controlled electric potential along its length and an intermediate layer (22) of solid electrically insulating material positioned between said inner and outer layers (20 and 21).

2. An SMES device according to claim 1, characterized in that the device further comprises a cryostat (6) in which the coil (1) and switch means (3) are enclosed.

3. An SMES device according to claim 1 or 2, characterized in that said superconducting means comprises high-temperature superconducting (HTS) means.

4. An SMES device according to claim 3, characterized in that said high-temperature superconducting (HTS) means comprises at least one layer (14) of high-temperature superconducting (HTS) material, cooling means (13) for cryogenically cooling the layer(s) (14) of HTS material below the critical temperature (T_c) of the HTS material and thermally insulating means (15) surrounding the layer(s) (14) of HTS material and the cooling means (13).

5. An SMES device according to claim 4, characterized in that the cooling means (13) comprises a support tube (13) through which cryogenic cooling fluid is passed and in that the at least one layer (14) of HTS material comprises HTS tape or conductors wound in a helical layer on said support tube (13).

6. An SMES device according to claim 4 or 5 characterized in that the thermally insulating means (15) comprises an annular space under vacuum and containing thermal insulation (18).

5 7. An SMES device according to any one of the preceding claims, characterized in that the semiconducting outer layer (21) has a resistivity of from 1 to 1000 ohm cm.

8. An SMES device according to claim 6, characterized in that the said outer layer (21) has a resistivity of from 10 to 500 ohm cm, preferably from 10 to 100 ohm cm.

10 9. An SMES device according to any one of the preceding claims, characterized in that the resistance per axial unit length of the semiconducting outer layer (21) is from 5 to 50,000 ohm.m⁻¹.

15 10. An SMES device according to any one of claims 1 to 8, characterized in that the resistance per axial unit of length of the semiconducting outer layer (21) is from 500 to 25,000 ohm.m⁻¹, preferably from 2,500 to 5,000 ohm.m⁻¹.

20 11. An SMES device according to any one of the preceding claims, characterized in that the semiconducting outer layer (21) is contacted by conductor means at said controlled electric potential at spaced apart regions along its length, adjacent contact regions being sufficiently close together that the voltages of mid-points between adjacent contact regions are insufficient for corona discharges to occur within the electrically insulating means.

25 12. An SMES device according to any one of the preceding claims, characterised in that said controlled electric potential is at or close to earth potential.

30 13. An SMES device according to any one of the preceding claims, characterised in that the said intermediate layer (22) is in close mechanical contact with each of said inner and outer layers (20 and 21).

14. An SMES device according to any one of claims 1 to 12, characterised in that the said intermediate layer (22) is joined to each of said inner and outer layers (20 and 21).

15. An SMES device according to any one of the preceding claims, characterised in that the strength of the adhesion between the said intermediate layer (22) and each of the semiconducting inner and outer layers (20, 21) is of the same order of magnitude as the intrinsic strength of the material of the intermediate layer.

16. An SMES device according to claim 14 or 15, characterised in that the said layers (20-22) are joined together by extrusion.

17. An SMES device according to claim 16, characterised in that the inner and outer layers (20, 21) of semiconducting material and the insulating intermediate layer (22) are applied together over the superconducting means through a multi layer extrusion die.

18. An SMES device according to any one of the preceding claims, characterised in that said inner layer (20) comprises a first plastics material having first electrically conductive particles dispersed therein, said outer layer (21) comprises a second plastics material having second electrically conductive particles dispersed therein and said intermediate layer (22) comprises a third plastics material.

19. An SMES device according to claim 18, characterized in that each of said first, second and third plastics materials comprises an ethylene butyl acrylate copolymer rubber, an ethylene-propylene-diene monomer rubber (EPDM) or an ethylene-propylene copolymer rubber (EPR), LDPE, HDPE, PP, PB, PMB XLPE, EPR or silicone rubber.

20. An SMES device according to claim 18 or 19, characterized in that said first, second and third plastics materials have at least substantially the same coefficients of thermal expansion.

21. An SMES device according to claim 18, 19 or 20 characterized in that said first, second and third plastics materials are the same material.

22. An electric power transmission system comprising an SMES device according to any one of the preceding claims connected to a high voltage source.

23. A high voltage system comprising an SMES device, characterized in that the SMES device has superconducting conductor means which is insulated against high voltage by an electric insulation system arranged concentrically around the conductor means.

24. A high voltage system according to claim 23, characterised in that the high voltage system comprises a high voltage network and that the SMES device is directly connected to the high voltage network without an intermediate transformer.

25. A high voltage system according to claim 24, characterized in that the network is a high voltage dc network.

26. A high voltage system according to claim 25, characterized in that the dc network is at a voltage exceeding 10 kV.

27. A high voltage system according to claim 24, characterized in that the SMES device is coupled to a high voltage ac network via a converter.

28. A high voltage system according to claim 25, comprising several ac networks connected via the dc network and the SMES device, the dc network being connected to the ac networks so that the SMES device can provide the ac networks with power.

29. A high voltage system according to any one of claims 23 to 28, characterized in that the SMES device comprises a coil.

30. A high voltage system according to any one of claims 23 to 28, characterized in that the SMES device comprises a cable without turns.

31. A high voltage system according to claim 27 of claim 29 when dependent on claim 27, characterized in that the SMES is one part of a bipolar dc link.

32. A high voltage system according to any one of claims 23 to 31, characterized in that said insulation system is extruded around the conductor means and comprises a first integral part forming an inner layer in electric contact with the conductor means and having semiconducting properties, a second integral part forming an outer layer around the insulation and having semiconducting properties and an insulating integral third part between the first and second integral parts.

33. A high voltage system according to an one of claims 23 to 31, characterized in that said insulation system comprises an all-synthetic film wound in overlapping layers around the conductor means with an inner part in electric contact with the conductor means and having semiconducting properties, an electrically insulating intermediate part and an outer part surrounding the intermediate part and having semiconducting properties.

34. A high voltage system according to any of claims 23 to 31, characterized in that said insulation system comprising one or more of a cellulose-based, synthetic paper or non-woven fibre material, co-lapped or laminated with a synthetic film and having an inner part in electric contact with the conductor means and having semiconducting properties, an electrically insulating intermediate part and an outer part around said intermediate part and having semiconducting properties.

35. A high voltage system according to claim 32, 33 or 34, characterized in that a cooling medium for cooling said superconductive conductor is arranged to flow within the conductor means.

36. A high voltage system according to claim 32, 33 or 34 characterized in that a cooling medium for cooling said superconductive conductors is arranged outside of the conductor means.

5

\\PLATO\VOL2\DATA\atty\jfc\9847\0058\98470058.spec.doc

SUBSTITUTE SPECIFICATION

9847-0058-6XPCT

ENKEL 8359

TITLE OF THE INVENTION

MAGNETIC ENERGY STORAGE

CROSS REFERENCE TO RELATED PATENT DOCUMENTS

The present document is based on published international patent application No. WO 99/28921, the entire contents of which being incorporated herein by reference.

BACKGROUND OF THE INVENTIONTechnical FieldField of the Invention:

This invention relates to a superconducting magnetic energy storage (SMES) device of the kind comprising including a coil for connection in series with a voltage source, e.g. a DCde voltage source, and wound from a superconducting cable having a superconducting means which, in use, is maintained at cryogenic temperatures below its critical temperature (T_c) and which is surrounded by electrical insulation, and a switch means for short-circuiting the coil. Although the invention primarily relates to high-temperature superconducting cables, the invention is also applicable to low-temperature superconducting cables because of the high magnetic field in magnetic energy storage.

Background of the InventionDiscussion of the Background:

The concept of superconducting magnetic energy storage (SMES) is well known. The principle of SMES is that energy is stored as magnetic energy in a coil having an inductance L , the amount of energy stored being given by $\frac{1}{2} L I^2$, where I is the DCde current.

The inductance L of a coil is given through the well-known relationship:

$$L = (\mu_0 \mu_r N^2 A) / l$$

where $\mu_0 = 4\pi \times 10^{-7}$ As/Vm, μ_r is the permeability of material in the magnetic circuit of a solenoid (which is 1 for air and around 10000 or higher for oriented laminated quality steel, provided the magnetic flux density B is sufficiently low), N is the number of windings, A is the cross-sectional area and l the length of the coil.

Since the magnetic energy E to be stored in a SMES device is $E = \frac{1}{2} L I^2$, it is evident that both current and inductance should be maximized. The maximum current is given through the properties of a superconductor at given temperature, magnetic field, and current density.

The inductance could be maximized by utilising a magnetic material in the magnetic circuit having a high permeability. Unfortunately, there are no known materials having a high permeability at high flux densities. In fact, at B around 2 Tesla, even the best materials go into saturation and, in addition, core losses (hysteresis and eddy) increase drastically in the saturation region. If the magnetic moments of a material are perfectly aligned, it is theoretically possible to reach a maximum flux density of 2.12 Tesla for iron. Due to the high currents of superconductors, the flux densities are also high, in fact densities of 5 T and more are not uncommon. Thus magnetic material should not be included in the magnetic circuit, at least not in regions of high B . In general, μ_r is then equal to one.

The inductance can also be increased by choosing a high number of windings N . If a solenoid is wound, then the winding density, that is the number of windings per unit length, is determined by the cross-sectional area of the conductor and its insulation.

The ratio of cross-sectional area to length is also an important parameter for the inductance. The aim should be to achieve a large cross-section and a short coil length. Thus pancake or disk windings are often designed as a preferred coil for achieving high inductances.

SMES devices have a high efficiency and high energy density compared with competing systems for storing energy. SMES devices can have a rapid response to demands of storing or discharging. In addition, SEES devices can be used not only for load-levelling but also for load-following, for spinning reserve, for transient stabilization, and for synchronous resonance damping. SMES can provide not only energy savings but also a larger freedom of power system operation.

Normally SMES devices are built for storing energy up to about 1 MW, but there is a demand for SMES devices with higher energy storage capability. Current solutions for larger SMES devices involve oversizing of equipment and the usage of multiple feeders connected to different transmission systems.

Conventional SMES devices operate with high current sources at low voltages. When used in an AC power system, an AC/DC converter can be used for converting the power to and from the SMES device. Operation of SMES devices connected to power networks will include a transformer.

A SMES device is normally built as a coil. In order to maximize the storage capability, the inductance should be as high as possible. Therefore, the superconductor is wound into a pancake, for example a 4 T background coil for SMES as described in "Design and construction of the 4 T background coil for the navy SMES cable test apparatus", IEEE Transactions on Applied Superconductivity, Vol 7, No 2, June 1997. The SMES devices are normally connected to voltages of up to about 500 V and currents of around 1000 A.

A large SMES device for 30MW is described in IEEE Transactions on Applied Superconductivity, Vol 7, No. 2, June 1997 in the article "Quench Protection and Stagnant Normal Zones in a Large Cryostable SMES," and involves a coil assembled from a multiple double pancake structure. The application of this SMES device requires a high power discharge and the operating voltage is desired to be up to 3.4 kV.

Another method of storing magnetic energy can be by winding the conductor directly as a solenoid. An example of a test coil is described in "Design, manufacturing and cold test of superconducting coil and its cryostat for SMES applications", IEEE Transactions on Applied Superconductivity, Vol 7, No. 2, June 1997, where a solenoid consists of a formed from a NbTi conductor with 4500 turns, 30 layers, and an inner winding radius of 120 mm.

SUMMARY OF THE INVENTION

An aim of the present invention is to have a high voltage system comprising including an SMES device, where superconducting conductors of the SMES device are insulated against high voltage and the insulation is concentric around the conductors.

According to one aspect of the present invention there is provided a SMES device of the kind referred to, characterized in that the said electrical insulation ~~comprises~~ includes an inner layer of semiconducting material electrically connected to said superconducting ~~means~~, an outer layer of semiconducting material at a controlled electric potential, e.g. earth potential, along its length and an intermediate layer of solid electrically insulating material positioned between said inner and outer layers.

In this specification the term "semiconducting material" ~~mean~~ indicates a material which has a considerably lower conductivity than an electrical conductor but which does not have such a low conductivity that it is an electrical insulator. Suitably, but not exclusively, a "semiconducting material" should have a volume resistivity of from $1 \cdot 10^5 \Omega \cdot \text{cm}$ preferably from $1 \cdot 10^3 \Omega \cdot \text{cm}$, more preferably $10 \cdot 500 \Omega \cdot \text{cm}$, and most preferably $10 \cdot 100 \Omega \cdot \text{cm}$, typically $20 \Omega \cdot \text{cm}$.

The present invention is not limited to high temperature superconductivity. Due to the high magnetic field in magnetic energy storage, low temperature superconductors are still attractive, even though they require cryostats operating between 1-15 K, depending on the type of low temperature superconductor utilized. Well-known examples are based on Niobium, such as NbTi, Nb₃Sn and Nb₃Al.

Other examples are V₃Ga and Nb₃Ge. The most common superconductor used is NbTi which can be utilized in magnetic field densities up to approximately 9 T at 4.2 K (or 11 T at 1.8 K). For higher field densities, NbTi cannot be used and is replaced by Nb₃Sn.

An SMES device according to the invention is made from cable-like conductors which can be manufactured according to conventional principles of cable manufacturing. The insulation is such that it can withstand high voltages in the range of 1 kV and upwards to the voltages used for high voltage ~~DC~~ ac current transmission.

The invention allows a high voltage system ~~comprising that includes~~ comprising an SMES device. The SMES device can be coupled to a high voltage network. This ~~means that allows~~ enables load-following ~~to be performed can be effected~~ on a transmission or distribution network and not only for a specific use within lower voltages as is the case with the SMES devices of today. This opens up ~~the possibilities to use of using~~ the possibility of using a SMES for storing energy to smooth load variations in a high voltage network on, for example, a day-night basis or an east-west basis. Also, ~~an~~ SMES device operating at a high voltage can be capable of injecting large

amounts of energy into a system ~~in~~ under a short time, that is injecting a large amount of real power, which will allow for good control of the system.

The present invention ~~provides~~ allows a high voltage system ~~comprising that includes~~ an SMES system which can be directly coupled to a high voltage of up to 800 kV and even above without the need to transform the voltage down. This can be achieved by insulating the superconducting ~~means~~ with an insulation system that can withstand high voltages. Such insulation systems are known, for example, from high voltage ~~DC~~ de transmission systems.

A specific advantage of the present invention is that, since the SMES device operates at high voltage, the current can be reduced for a given power density. Thus, by- way of example only, for a conventional SMES device operating at 20 kV, a similarly powered SMES device according to the invention can operate at about 150 kV resulting in a reduction of the current of about 7.5 times. Since the magnetic force in the cable is proportional to current x magnetic flux density (B), the magnetic force is effectively reduced about 7.5 times. Furthermore, the amount of semiconductor saved will, in this example, amount to approximately 7.5 times. Similarly, the cooling losses will be essentially reduced. All these factors improve the economic attractiveness of the SMES device.

A further advantage with an SMES device operating at high voltages is that charging and discharging can be rapid. It is normally very time-consuming to charge, at least larger SMES devices, and by ~~being able to~~ connecting the SMES device to a high voltage the charging time can be substantially reduced. Also, the power that can be delivered from the SMES device is increased by increasing the voltage ~~across~~ over the SMES device.

Another advantage is that an SMES device can be installed close to a large power generating unit, such as a nuclear power station. ~~During~~ At a rapid close-down of a nuclear power station, there are great strains on the network. These can be effectively smoothed by a high voltage SMES device that is able to inject the corresponding power into the system and then allow for a slow ramp down of the power.

Another advantage of a high voltage SMES device is that there is no need for a transformer to be provided for transforming power to and from the SMES device. The SMES device can be directly coupled to a transmission or distribution network without intermediate step-up transformers. The elimination of transformers in the system leads to higher efficiency

of the system. The performance of the SMES system will be greatly improved by being able to connect the SMES device directly to a power network and by the increased efficiency that is created by the reduction of the number of components in the system.

Another advantage is that the SMES device is wholly electrically insulated in such a way that there is no electric field outside the superconducting cable. This facilitates the design of the mechanical structure holding the cables. It is possible to scale up the SMES device with fewer problems with the mechanical stability of the SMES device.

Another advantage of an SMES device with high voltage insulation is that discharges that normally occur in the electric system are prevented by the insulation system and the risk of bubble formation in the cooling medium is therefore reduced.

By connecting the coil directly to a high voltage DC source, e.g. to a high voltage AC/DC converter, charging and discharging of the coil is simplified. In particular, in an AC power transmission system, the need to transform the AC voltage down prior to connection to an AC/DC converter is eliminated. By holding the semiconducting outer layer at a controlled electric potential, e.g. ground or earth potential along its length, e.g. at spaced apart intervals along its length, the electric field generated by the superconducting means is contained within the electrical insulation.

Conveniently the coil and switch means are enclosed within a cryostat for maintaining the temperature of the superconducting means below its critical temperature (T_c).

Alternatively, or in addition, the superconducting means may be internally cooled by a cryogenic fluid, e.g. liquid nitrogen, and externally thermally insulated. For example, thermal insulation may conveniently be provided between the superconducting means and the surrounding electrical insulation. In some cases, the electrical insulation can also function as thermal insulation.

By only using, for the intermediate layer, only materials which can be manufactured with few, if any, defects and by providing the intermediate layer with the spaced apart inner and outer layers of semiconducting material having similar thermal properties, thermal and electrical loads within the insulation are reduced. In particular, the insulating intermediate layer and the semiconducting inner and outer layers should have at least substantially the same coefficients of thermal expansion (α) so that defects caused by different thermal expansions when the layers are subjected to heating or cooling will not arise. Ideally, the

electrical insulation is of substantially unitary construction. The layers of the insulation may be in close mechanical contact but are preferably joined or united together. Preferably, for example, the radially adjacent layers will be extruded together around the superconducting means. The superconducting cable is flexible at normal ambient temperatures and thus can be bent or flexed into its desired winding shape prior to operation at cryogenic temperatures.

Conveniently the electrically insulating intermediate layer ~~comprises~~ is formed from a solid thermoplastics material, such as low or high density polyethylene (LDPE or HDPE)), polypropylene (PP), polybutylene (PB), polymethylpentene (PMP), ethylene (ethyl) acrylate copolymer, cross-linked materials, such as cross-linked polyethylene (XLPE), or rubber insulation, such as ethylene propylene rubber (EPR) or silicone rubber. The semiconducting inner and outer layers may ~~comprise~~ include a similar material to the intermediate layer but with conducting particles, such as carbon black, soot, or metallic particles, embedded therein. Generally, it has been found that a particular insulating material, such as EPR, has similar mechanical properties when containing no, or some, carbon particles.

The screens of semiconducting inner and outer layers form substantially equipotential surfaces on the inside and outside of the insulating intermediate layer so that the electric field, in the case of concentric semiconducting and insulating layers, is substantially radial and confined within the intermediate layer. In particular, the semiconducting inner layer is arranged to be in electrical contact with, and to be at the same potential as, the superconducting means ~~that~~ which it surrounds. The semiconducting outer layer is designed to act as a screen to prevent losses caused by induced voltages. Induced voltages could be reduced by increasing the resistance of the outer layer. Since the thickness of the semiconducting layer cannot be reduced below a certain minimum thickness, the resistance can only be reduced by selecting a material for the layer having a higher resistivity.

However, if the resistivity of the semiconducting outer layer is too great the voltage potential between adjacent spaced apart points at a controlled, e.g. earth, potential will become sufficiently high as to risk the occurrence of corona discharge with consequent erosion of the insulating and semiconducting layers. The semiconducting outer layer is therefore a compromise between a conductor having low resistance and high induced voltage losses but which is easily connected to a controlled electric potential, typically earth or ground potential, and an insulator which has high resistance with low induced voltage losses but which needs

to be connected to the controlled electric potential along its length. Thus the resistivity ρ_x of the semiconducting outer layer should be within the range $\rho_{\min} < \rho_x < \rho_{\max}$, where ρ_{\min} is determined by permissible power loss caused by eddy current losses and resistive losses caused by voltages induced by magnetic flux and ρ_{\max} is determined by the requirement for no corona or glow discharge.

If the semiconducting outer layer is earthed, or connected to some other controlled electric potential, at spaced apart intervals along its length, there is no need for an outer metal shield and protective sheath to surround semiconducting outer layer. The diameter of the cable is thus reduced allowing more turns to be provided for a given size of winding.

The electrical insulation can be extruded over the superconductor ~~ing means~~ or a lapped concept can be used. This can include both the semiconducting layers and the electrically insulating layer. An insulation can be made of an all-synthetic film with inner and outer semiconducting layers made of a polymeric thin film of, for example, PP, PET, LDPE or HDPE with embedded conducting particles, such as carbon black or metallic particles.

For the lapped concept, a sufficiently thin film will have butt gaps smaller than the so-called Paschen minima, thus rendering liquid impregnation unnecessary. A dry, wound multilayer thin film insulation has also good thermal properties and can be combined with a superconducting pipe as an electric conductor and have coolant, such as liquid nitrogen, pumped through the pipe.

Another example of electrical insulation is similar to a conventional cellulose based cable, where a thin cellulose based or synthetic paper or non-woven material is lap wound around a conductor. In this case the semi-conducting layers can be made of cellulose paper or nonwoven material made from fibres of insulating material and with conducting particles embedded. The insulating layer can be made from the same base material or another material can be used.

Another example is obtained by combining film and fibrous insulating material, either as a laminate or as co-lapped. An example of this insulation system is the commercially available so-called paper polypropylene laminate, PPLP, but several other combinations of film and fibrous parts are possible. In these systems various impregnations such as mineral oil or liquid nitrogen can be used.

The superconductor ~~ing means may comprise be formed from~~ low temperature semiconductors, but most preferably ~~comprises is formed from~~ high-temperature superconducting (HTS) materials, for example HTS wires or tape helically wound on an inner tube. The HTS tape conveniently ~~comprises is~~ silver-sheathed BSCCO-2212 or BSCCO-2223 (where the numerals indicate the number of atoms of each element in the $[\text{Bi}, \text{Pb}]_x \text{Sr}_2 \text{Ca}_2 \text{Cu}_3 \text{O}_x$ molecule) and hereinafter such HTS tapes will be referred to as "BSCCO tape(s)". BSCCO tapes are made by encasing fine filaments of the oxide superconductor in a silver or silver oxide matrix by a powder-in-tube (PIT) draw, roll, sinter and roll process. Alternatively the tapes may be formed by a surface coating process. In either case the oxide is melted and resolidified as a final process step. Other HTS tapes, such as TiBaCaCuO (TBCCO-1223) and YBaCuO (YBCO-123) have been made by various surface coating or surface deposition techniques. Ideally an HTS wire should have a current density beyond $j_c \sim 10^5 \text{ Acm}^{-2}$ at operation temperatures from 65 K, but preferably above 77 K. The filling factor of ITS in the matrix needs to be high so that the engineering current density $j_e \geq 10^4 \text{ Acm}^{-2}$. j_c should not drastically decrease with applied fields within the Tesla range. The helically wound HTS tape is cooled to below the critical temperature T_c of the HTS by a cooling fluid, preferably liquid nitrogen, passing through the inner support tube.

A cryostat layer may be arranged around the helically wound HTS tape to thermally insulate the cooled HTS tape from the electrically insulating material. Alternatively, however, the cryostat may be dispensed with. In this latter case, the electrically insulating material may be applied directly over the superconductor ~~ing means~~. Alternatively, a space may be provided between the superconductor ~~ing means~~ and the surrounding insulating material, the space either being a void space or a space filled with compressible material, such as a highly compressible foamed material. The space reduces expansion/contraction forces on the insulation system during heating from/cooling to cryogenic temperatures. If the space is filled with compressible material, the latter can be made semiconducting to ensure electrical contact between the semiconducting inner layer and the superconductor ~~ing means~~.

Other designs of superconductors ~~ing means~~ are possible, the invention being directed to transformer windings, formed from superconducting cables of any suitable design having a surrounding electrical insulation of the type described above. For example other types of superconductors ~~ing means may comprise include~~, in addition to internally cooled HTS

material, externally cooled HTS material or externally and internally cooled HTS material. In the latter type of HTS cable, two concentric HTS conductors separated by cryogenic insulation and cooled by liquid nitrogen are used to transmit electricity. The outer conductor acts as the return path and both HTS conductors may be formed of one or many layers of HTS tape for carrying the required current. The inner conductor may ~~comprise~~ include HTS tape wound on a tubular support through which liquid nitrogen is passed. The outer conductor is cooled externally by liquid nitrogen and the whole assembly may be surrounded by a thermally insulating cryostat.

According to another aspect of the present invention there is provided an electric power transmission system characterized in that an SMES device according to said one aspect is connected to a high voltage source, preferably a high voltage DC source.

The SMES device may be in the form of a cable and preferably a cable with high inductance. The electrical insulation of the cable can be made of conductor tape or wire with several layers where all layers are wound in the same direction, instead of as conventionally winding the layers in opposite direction in order to compensate for the inductance. Such cable with an extruded insulation system could be directly incorporated into a transmission line, for example as one line of a bipolar DC system.

It is also possible to use such cable to build up a solenoid with high inductance.

The invention as herein described can also be used with conventional low-temperature superconducting materials and with coolants such as liquid helium.

It is also possible to use the invention with an AC source. The losses are larger for an AC SMES device but if the losses are acceptable for the system to be designed, the principle of the invention is applicable.

BRIEF DESCRIPTION OF THE DRAWINGS

Embodiments of the invention will now be described, by way of example only, with particular reference to the accompanying drawings, in which:

Figure 1 is a circuit diagram of an SMES device according to the present invention;

Figure 2 is a schematic sectional view, on an enlarged scale, through part of one embodiment of a high-temperature superconducting cable from which the coil of the SMES device of Figure 1 is wound;

Figure 3 is a schematic sectional view, on an enlarged scale, of another embodiment of high temperature superconducting cable from which the coil of the SMES device of Figure 1 can be wound;

Figure 4 is a schematic view of two high voltage AC networks coupled together via a high voltage DC network and incorporating an SMES device on the DC side;

Figure 5 is a schematic view of an SMES incorporated in a high voltage DC network; and

Figure 6 is a schematic view of two convertor stations with voltage source converters and combined with a high voltage bipolar DC link.

DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS

Figure 1 shows a coil 1 having an inductance L formed of high-temperature (T_c) superconducting (HTS) cable 12 (see Figure 2) which is connected with a high DC voltage source 2, e.g. the DC side of a high voltage AC/DC converter connected to an AC power transmission line. A switch 3 is connected in parallel with the high DC voltage source 2 and is operable to short-circuit the coil 1.

When the coil 1 is connected to the dc voltage source 2, a DC current I flows and charges the coil. Due to the high current density of the superconducting cable and its virtually zero resistance, energy is simply stored by closing the switch 3 and short-circuiting the coil. The energy in the coil is stored as magnetic energy having a value of $\frac{1}{2}IL^2$. The coil 1 is thus able to store electrical energy and to provide electrical power at a fast rate when required at times of peak consumption.

The superconducting cable 12 from which the coil 1 is formed ~~comprises~~ includes an inner tubular support 13, e.g. of copper or a highly resistive metal, such as copper-nickel alloy, on which is helically wound elongate HTS material, for example BSCCO tape or the like, to form a superconducting layer 14 around the tubular support 13. A cryostat 15, arranged outside the superconducting layer, ~~comprises~~ includes two spaced apart flexible corrugated metal tubes 16 and 17. The space between the tubes 16 and 17 is maintained under vacuum and contains thermal superinsulation 18. Liquid nitrogen, or other cooling fluid, is passed along the tubular support 13 to cool the surrounding superconducting layer 14 to

below its critical superconducting temperature T_c . The tubular support 13, superconducting layer 14 and cryostat 15 together constitute ~~the superconductor ing means~~ of the cable 12.

Solid electrical insulation, e.g. of plastics material, is arranged outside the superconducting ~~ing means~~. The electrical insulation ~~comprises~~ includes an inner semiconducting layer 20, an outer semiconducting layer 21, and, sandwiched between these semiconducting layers, an insulating layer 22. The layers 20-22 preferably ~~comprise are~~ formed from thermoplastics materials providing a substantially unitary construction. The layers may be in close mechanical contact with each other but are preferably solidly connected to each other at their interfaces. Conveniently, these thermoplastics materials have similar coefficients of thermal expansion and are preferably extruded together around the inner superconducting ~~ing means~~. The electrical insulation conveniently has an electric field stress of no more than 0.2 kV/mm.

By way of example only, the solid insulating layer 22 may ~~comprise be formed from~~ cross-linked polyethylene (XLPE). Alternatively, however, the solid insulating layer may ~~comprise be formed from~~ other cross-linked materials, low density polyethylene (LDPE), high density polyethylene (HDPE), polypropylene (PP), polymethylpentene (PMP), ethylene (ethyl) acrylate copolymer, or rubber insulation, such as ethylene propylene rubber (EPR), ethylene-propylene-diene monomer (EPDM), or silicone rubber. The semiconducting material of the inner and outer layers 20 and 21 may ~~comprise be formed from~~, for example, a base polymer of the same material as the solid insulating layer 22 and highly electrically conductive particles, e.g. particles of carbon black or metallic particles, embedded in the base polymer. The volume resistivity of these semiconducting layers, typically about 20 ohm cm, may be adjusted as required by varying the type and proportion of carbon black added to the base polymer. The following gives an example of the way in which resistivity can be varied using different types and quantities of carbon black.

<u>Base Polymer</u>	<u>Carbon Black Type</u>	<u>Carbon Black Quantity (%)</u>	<u>Volume Resistivity $\Omega \cdot \text{cm}$</u>
Ethylene vinyl acetate copolymer/nitrite rubber	EC carbon black	-15	350-400
"	P-carbon black	-37	70-10
"	Extra conducting carbon black, type I	-35	40-50
"	Extra conducting carbon black, type II	-33	30-60
Butyl grafted polyethylene	"	-25	7-10
Ethylene butyl acrylate copolymer	Acetylene carbon black	-35	40-50
"	P carbon black	-38	5-10
Ethylene propene rubber	Extra conducting carbon black	-35	200-400

The outer semiconductive layer 21 is connected to a desired controlled electric potential, e.g. earth potential, at spaced apart regions along its length, the specific spacing apart of adjacent controlled potential or earthing points being dependent on the resistivity of the layer 21.

The semiconducting layer 21 acts as a static shield and by controlling the electric potential of the outer layer, e.g. to earth potential, it is ensured that the electric field of the superconducting cable is retained within the solid insulation between the semiconducting layers 20 and 21. Losses caused by induced voltages in the layer 21 are reduced by increasing the resistance of the layer 21. However, since the layer 21 must be at least of a certain minimum thickness, e.g. no less than 0.8 mm, the resistance can only be increased by selecting the material of the layer to have a relatively high resistivity. The resistivity cannot be increased too much, however, else the voltage of the layer 21 mid-way between two adjacent earthing points will be too high with the associated risk of corona discharges occurring.

Instead of, or in addition to, internally cryogenically cooling the HTS cable 12, the coil 1 and switch 3 may be enclosed within a cryostat 6 (shown schematically in dashed lines in Figure 1) for keeping the coil 1 at temperatures below the critical temperature of the superconducting means. In this case, the thermally insulating cryostat 15 need not be included in the HTS cable described above with reference to Figure 2. Figure 3 shows a typical design of cable having no cryostat 15. In this case, the electrical insulation, provided by the layers 20-22, is extruded directly over the superconducting layer 14 wound on the tubular support 13. Although not shown, an annular gap may be provided between the electric insulation and the layer 14 to cater for the differences in thermal expansion/contraction of the electrical insulation and the layer 14. This annular gap could be a void space or could be filled with compressible material, such as highly compressible foam material. If such an annular gap is provided, the semiconducting inner layer 20 is preferably placed in electrical contact with the superconducting layer 14. For example, if the compressible foam material is included in the annular gap, the foam material may be made semiconducting.

Figure 4 shows a high voltage system ~~comprising including~~ two high voltage AC networks, N1 and N2, T1Y and T2Y are converter transformers in Y/Y coupling and T1D and T2D are converter transformers in Y/D coupling. SCR11, SCR12, SCR21 and SCR22 are series-connected 6-pulse line-commutated bridge-connected converters. The converters SCR11 and SCR12 are linked with the converters SCR21 and SCR22 via a DC link DCL which ~~comprises includes~~ an energy storage device in the form of a superconducting magnetic storage device SMES.

The voltage ~~across over~~ the converters SCR11 and SCR12 is U1 and the voltage ~~across over~~ converters SCR21 and SCR22 is U2. U1 and U2 are each controlled in a conventional manner by control equipment (not shown) connected with its respective converter. The current I_d runs through the DC link DCL and the device SMES.

In the system shown in Figure 4, $U_1 - U_2 = L \cdot dI/dt$, which ~~means indicates that~~ the charging and discharging of the device SMES can be controlled by the control angles of the converters. One or both converters can charge or discharge the SMES. By controlling $U_1=U_2$, the content of energy of the SMES can be unaffected.

Figure 5 shows the same basic high voltage system as Figure 4. In Figure 5, however, the superconducting magnetic energy storage device SMES is used as a storage device for the ac network N1 and is charged via the converters SCR11 and SCR12, with switch S1 closed and switch S2 open. During charging of the device SMES, the current through the coil can be measured and charging continues until a nominal value is reached. When the SMES is fully charged, S1 opens and S2 closes. For feeding the network N1, for example in the case of a power loss on the network, S1 closes and S2 is opened.

In the Figure 5 system, the superconducting magnetic energy storage device SMES is part of a high voltage DCde transmission system with a DCde link. A pole control device, PCM, is needed when providing the network N2 with power.

Figure 6 shows a high voltage system having two voltage-controlled converters VSC1 and VSC2, which are connected via a DCde link in the form of a double cable TC. The DC de-link is bipolar in that the capacitors C11 and C12 and the capacitors C21 and C22 are respectively connected to ground at their connecting point. A superconducting magnetic energy storage device SMES is arranged at one pole of the converter VSC1. It is also possible to arrange the superconducting magnetic energy storage device in the form of a cable as one part of the bipolar dc link.

Although the invention has been described with specific reference to an SMES device having a coil for connection in series with a DCde voltage source, the invention is also intended to embrace connection of the coil to an ACae voltage source.

The term "high voltage" used in this specification is intended to mean up to 800 kV or even higher. An SMES device may be connected to such high voltage networks and at high powers of up to 1000 MVA. At high voltages, partial discharges, or PD, constitute a serious problem for known insulation systems. If cavities or pores are present in the insulation, internal corona discharges may arise whereby the insulating material is gradually degraded eventually leading to breakdown of the insulation. The electric load on the electrical insulation of the superconductor ~~ing means~~ of an SMES device according to the present invention is reduced by ensuring that the inner portion of the electrical insulation is at substantially the same electric potential as the superconductor ~~ing means~~ and that the outer portion of the electrical insulation is at a controlled potential. Thus the electric field is distributed substantially uniformly over the thickness of the electrically insulating portion of

the insulation between the inner and outer portions. By having materials for the electrical insulation with similar thermal properties and with few defects in the layers or portions, the possibility of PD is reduced.

An additional advantage of the present invention is that, since the SMES device operates at high voltage, the current can be reduced for a given power density. Thus for a conventional SMES device operating at 20 kV, a similarly powered SMES device according to the invention can operate at about 150 kV resulting in a reduction of the current of about 7.5 times. Since the magnetic force in the cable is proportional to current x magnetic flux density (B), the magnetic force is effectively reduced about 7.5 times. Furthermore, the amount of semiconductor saved will, in this example, amount to approximately 7.5 times. Similarly, the cooling losses will be essentially reduced. All these factors improve the economic attractiveness of the SMES device.

The present invention is not limited to high temperature superconductivity. Due to the high magnetic field in magnetic energy storage, low temperature superconductors are still attractive, even though they require cryostats operating between 1-15 K, depending on the type of low temperature superconductor utilized. Well-known examples are based on niobium, such as NbTi, Nb₃Sn and Nb₃Al. Other examples are V₃Ga and Nb₃Ge. The most common superconductor used is NbTi which can be utilized in magnetic field densities up to approximately 9 T at 4.2 K (or 11 T at 1.8 K). For higher field densities, NbTi cannot be used and is replaced by Nb₃Sn.

CLAIMS:

1. An SMES device comprising a coil (1) for connection in series with a voltage source (2), e.g. a dc voltage source, and wound from a superconducting cable (12) having superconducting means (14) which, in use, is maintained at cryogenic temperatures below its critical temperature (T_c) and which is surrounded by electrical insulation (20-22), and switch means (3) for shortcircuiting the coil (1), characterized in that the said electrical insulation comprises an inner layer (20) of semiconducting material electrically connected to said superconducting means, an outer layer (21) of semiconducting material at a controlled electric potential along its length and an intermediate layer (22) of solid electrically insulating material positioned between said inner and outer layers (20 and 21).

2. An SMES device according to claim 1, characterized in that the device further comprises a cryostat (6) in which the coil (1) and switch means (3) are enclosed.

3. An SMES device according to claim 1 or 2, characterized in that said superconducting means comprises high-temperature superconducting (HTS) means.

4. An SMES device according to claim 3, characterized in that said high-temperature superconducting (HTS) means comprises at least one layer (14) of high-temperature superconducting (HTS) material, cooling means (13) for cryogenically cooling the layer(s) (14) of HTS material below the critical temperature (T_c) of the HTS material and thermally insulating means (15) surrounding the layer(s) (14) of HTS material and the cooling means (13).

5. An SMES device according to claim 4, characterized in that the cooling means (13) comprises a support tube (13) through which cryogenic cooling fluid is passed and in that the at least one layer (14) of HTS material comprises HTS tape or conductors wound in a helical layer on said support tube (13).

6. An SMES device according to claim 4 or 5 characterized in that the thermally insulating means (15) comprises an annular space under vacuum and containing thermal insulation (18).

7. An SMES device according to any one of the preceding claims, characterized in that the semiconducting outer layer (21) has a resistivity of from 1 to 1000 ohm cm.

8. An SMES device according to claim 6, characterized in that the said outer layer (21) has a resistivity of from 10 to 500 ohm cm, preferably from 10 to 100 ohm cm.

9. An SMES device according to any one of the preceding claims, characterized in that the resistance per axial unit length of the semiconducting outer layer (21) is from 5 to 50,000 ohm.m⁻¹.

10. An SMES device according to any one of claims 1 to 8, characterized in that the resistance per axial unit of length of the semiconducting outer layer (21) is from 500 to 25,000 ohm.m⁻¹, preferably from 2,500 to 5,000 ohm.m⁻¹.

11. An SMES device according to any one of the preceding claims, characterized in that the semiconducting outer layer (21) is contacted by conductor means at said controlled electric potential at spaced apart regions along its length, adjacent contact regions being sufficiently close together that the voltages of mid-points between adjacent contact regions are insufficient for corona discharges to occur within the electrically insulating means.

12. An SMES device according to any one of the preceding claims, characterised in that said controlled electric potential is at or close to earth potential.

13. An SMES device according to any one of the preceding claims, characterised in that the said intermediate layer (22) is in close mechanical contact with each of said inner and outer layers (20 and 21).

14. An SMES device according to any one of claims 1 to 12, characterised in that the said intermediate layer (22) is joined to each of said inner and outer layers (20 and 21).

15. An SMES device according to any one of the preceding claims, characterised in that the strength of the adhesion between the said intermediate layer (22) and each of the semiconducting inner and outer layers (20, 21) is of the same order of magnitude as the intrinsic strength of the material of the intermediate layer.

16. An SMES device according to claim 14 or 15, characterised in that the said layers (20-22) are joined together by extrusion.

17. An SMES device according to claim 16, characterised in that the inner and outer layers (20, 21) of semiconducting material and the insulating intermediate layer (22) are applied together over the superconducting means through a multi layer extrusion die.

18. An SMES device according to any one of the preceding claims, characterised in that said inner layer (20) comprises a first plastics material having first electrically conductive particles dispersed therein, said outer layer (21) comprises a second plastics material having second electrically conductive particles dispersed therein and said intermediate layer (22) comprises a third plastics material.

19. An SMES device according to claim 18, characterized in that each of said first, second and third plastics materials comprises an ethylene butyl acrylate copolymer rubber, an ethylene-propylene-diene monomer rubber (EPDM) or an ethylene-propylene copolymer rubber (EPR), LDPE, HDPE, PP, PB, PMB XLPE, EPR or silicone rubber.

20. An SMES device according to claim 18 or 19, characterized in that said first, second and third plastics materials have at least substantially the same coefficients of thermal expansion.

21. An SMES device according to claim 18, 19 or 20 characterized in that said first, second and third plastics materials are the same material.

22. An electric power transmission system comprising an SMES device according to
5 any one of the preceding claims connected to a high voltage source.

23. A high voltage system comprising an SMES device, characterized in that the SMES device has superconducting conductor means which is insulated against high voltage by an electric insulation system arranged concentrically around the conductor means.

24. A high voltage system according to claim 23, characterised in that the high voltage system comprises a high voltage network and that the SMES device is directly connected to the high voltage network without an intermediate transformer.

25. A high voltage system according to claim 24, characterized in that the network is a high voltage dc network.

26. A high voltage system according to claim 25, characterized in that the dc network is at a voltage exceeding 10 kV.

27. A high voltage system according to claim 24, characterized in that the SMES device is coupled to a high voltage ac network via a converter.

28. A high voltage system according to claim 25, comprising several ac networks connected via the dc network and the SMES device, the dc network being connected to the ac networks so that the SMES device can provide the ac networks with power.

29. A high voltage system according to any one of claims 23 to 28, characterized in that the SMES device comprises a coil.

30. A high voltage system according to any one of claims 23 to 28, characterized in that the SMES device comprises a cable without turns.

31. A high voltage system according to claim 27 of claim 29 when dependent on claim 27, characterized in that the SMES is one part of a bipolar dc link.

32. A high voltage system according to any one of claims 23 to 31, characterized in that said insulation system is extruded around the conductor means and comprises a first integral part forming an inner layer in electric contact with the conductor means and having semiconducting properties, a second integral part forming an outer layer around the insulation and having semiconducting properties and an insulating integral third part between the first and second integral parts.

33. A high voltage system according to an one of claims 23 to 31, characterized in that said insulation system comprises an all-synthetic film wound in overlapping layers around the conductor means with an inner part in electric contact with the conductor means and having semiconducting properties, an electrically insulating intermediate part and an outer part surrounding the intermediate part and having semiconducting properties.

34. A high voltage system according to any of claims 23 to 31, characterized in that said insulation system comprising one or more of a cellulose-based, synthetic paper or non-woven fibre material, co-lapped or laminated with a synthetic film and having an inner part in electric contact with the conductor means and having semiconducting properties, an electrically insulating intermediate part and an outer part around said intermediate part and having semiconducting properties.

35. A high voltage system according to claim 32, 33 or 34, characterized in that a cooling medium for cooling said superconductive conductor is arranged to flow within the conductor means.

36. A high voltage system according to claim 32, 33 or 34 characterized in that a cooling medium for cooling said superconductive conductors is arranged outside of the conductor means.

5

\\PLATO\VOL2\DATA\atty\jfc\9847\0058\98470058.spec.doc

I:\atty\bd\9847\98470058.pa

Magnetic Energy StorageTechnical Field

This invention relates to a superconducting magnetic energy storage (SMES) device of the kind comprising a coil for connection in series with a voltage source, e.g. a dc voltage source, and wound from a superconducting cable having superconducting means which, in use, is maintained at cryogenic temperatures below its critical temperature (T_c) and which is surrounded by electrical insulation, and switch means for short-circuiting the coil. Although the invention primarily relates to high-temperature superconducting cables, the invention is also applicable to low-temperature superconducting cables because of the high magnetic field in magnetic energy storage.

15 Background of the Invention

The concept of superconducting magnetic energy storage (SMES) is well known. The principle of SMES is that energy is stored as magnetic energy in a coil having an inductance L , the amount of energy stored being given by $\frac{1}{2} \cdot L \cdot I^2$, where I is the dc current.

The inductance L of a coil is given through the well-known relationship:

$$L = (\mu_0 \mu_r N^2 A) / l$$

where $\mu_0 = 4\pi \times 10^{-7}$ As/Vm, μ_r is the permeability of material in the magnetic circuit of a solenoid (which is 1 for air and around 10000 or higher for oriented laminated quality steel, provided the magnetic flux density B is sufficiently low), N is the number of windings, A is the cross-sectional area and l the length of the coil.

30 Since the magnetic energy E to be stored in a SMES device is $E = \frac{1}{2} \cdot L \cdot I^2$, it is evident that both current and inductance should be maximised. The maximum current is

- 2 -

given through the properties of a superconductor at given temperature, magnetic field and current density.

The inductance could be maximised by utilising a magnetic material in the magnetic circuit having a high permeability. Unfortunately, there are no known materials having a high permeability at high flux densities. In fact at B around 2 Tesla, even the best materials go into saturation and, in addition, core losses (hysteresis and eddy) increase drastically in the saturation region. If the magnetic moments of a material are perfectly aligned, it is theoretically possible to reach a maximum flux density of 2.12 Tesla for iron. Due to the high currents of superconductors, the flux densities are also high, in fact densities of 5 T and more are not uncommon. Thus magnetic material should not be included in the magnetic circuit, at least not in regions of high B. In general, μ_r is then equal to one.

The inductance can also be increased by choosing a high number of windings N. If a solenoid is wound, then the winding density, that is the number of windings per unit length, is determined by the cross-sectional area of the conductor and its insulation.

The ratio of cross-sectional area to length is also an important parameter for the inductance. The aim should be to achieve a large cross-section and a short coil length. Thus pancake or disk windings are often designed as a preferred coil for achieving high inductances.

SMES devices have a high efficiency and high energy density compared with competing systems for storing energy. SMES devices can have a rapid response to demands of storing or discharging. In addition SMES devices can be used not only for load-levelling but also for load-following, for spinning reverse, for transient stabilization and for synchronous resonance damping. SMES can provide not only

- 3 -

energy savings but also a larger freedom of power system operation.

Normally SMES devices are built for storing energy up to about 1 MW, but there is a demand for SMES devices with higher energy storage capability. Current solutions for larger SMES devices involve oversizing of equipment and the usage of multiple feeders connected to different transmission systems.

Conventional SMES devices operate with high current source at low voltage. When used in an ac power system an ac-dc converter can be used for converting the power to and from the SMES device. Operation of SMES devices connected to power networks will include a transformer.

A SMES device is normally built as a coil. In order to maximize the storage capability, the inductance should be as high as possible. Therefore, the superconductor is wound into a pancake, for example a 4 T background coil for SMES as described in "Design and construction of the 4 T background coil for the navy SMES cable test apparatus", IEEE Transactions on Applied Superconductivity, Vol 7, No 2, June 1997. The SMES devices are normally connected to voltages of up to about 500 V and currents of around 1000 A.

A large SMES device for 30MW is described in IEEE Transactions on Applied Superconductivity, Vol 7, No. 2, June 1997 in the article "Quench Protection and Stagnant Normal Zones in a Large Cryostable SMES" and involves a coil assembled from a multiple double pancake structure. The application of this SMES device requires a high power discharge and the operating voltage is desired to be up to 3.4 kV.

Another method of storing magnetic energy can be by winding the conductor directly as a solenoid. An example of a test coil is described in "Design, manufacturing and cold test of superconducting coil and its cryostat for SMES

- 4 -

applications", IEEE Transactions on Applied Superconductivity, Vol 7, No. 2, June 1997, where a solenoid consists of a NbTi conductor with 4500 turns, 30 layers and an inner winding radius of 120 mm.

5 Summary of Invention

An aim of the present invention is to have a high voltage system comprising an SMES device, where superconducting conductors of the SMES device are insulated against high voltage and the insulation is concentric around
10 the conductors.

According to one aspect of the present invention there is provided a SMES device of the kind referred to, characterised in that the said electrical insulation comprises an inner layer of semiconducting material
15 electrically connected to said superconducting means, an outer layer of semiconducting material at a controlled electric potential, e.g. earth potential, along its length and an intermediate layer of solid electrically insulating material positioned between said inner and outer layers.

20 In this specification the term "semiconducting material" means a material which has a considerably lower conductivity than an electrical conductor but which does not have such a low conductivity that it is an electrical insulator. Suitably, but not exclusively, a "semiconducting material" should have a volume resistivity of from
25 $1 \cdot 10^5 \Omega \cdot \text{cm}$, preferably from $1 \cdot 10^3 \Omega \cdot \text{cm}$, more preferably $10 \cdot 500 \Omega \cdot \text{cm}$ and most preferably $10 \cdot 100 \Omega \cdot \text{cm}$, typically $20 \Omega \cdot \text{cm}$.

The present invention is not limited to high temperature superconductivity. Due to the high magnetic
30 field in magnetic energy storage, low temperature superconductors are still attractive, even though they require cryostats operating between 1-15 K, depending on the type of low temperature superconductor utilised. Well known examples are based on Niobium, such as NbTi, Nb₃Sn and Nb₃Al.

- 5 -

Other examples are V_3Ga and Nb_3Ge . The most common superconductor used is $NbTi$ which can be utilised in magnetic field densities up to approximately 9 T at 4.2 K (or 11 T at 1.8 K). For higher field densities, $NbTi$ cannot be used and is replaced by Nb_3Sn .

An SMES device according to the invention is made from cable-like conductors which can be manufactured according to conventional principles of cable manufacturing. The insulation is such that it can withstand high voltages in the range of 1 kV and upwards to the voltages used for high voltage dc current transmission.

The invention allows a high voltage system comprising an SMES device. The SMES device can be coupled to a high voltage network. This means that load-following can be effected on a transmission or distribution network and not only for a specific use on lower voltage as is the case with the SMES devices of today. This opens up possibilities to use SMES for storing energy to smooth load variations in a high voltage network on, for example, day-night basis or east-west basis. Also, an SMES device on high voltage can be capable of injecting large amounts of energy into a system under a short time, that is injecting a large amount of real power, which will allow for good control of the system.

The present invention allows a high voltage system comprising an SMES system which can be directly coupled to a high voltage of up to 800 kV and even above without the need to transform the voltage down. This can be achieved by insulating the superconducting means with an insulation system that can withstand high voltages. Such insulation systems are known for example from high voltage dc transmission systems.

A specific advantage of the present invention is that, since the SMES device operates at high voltage, the current can be reduced for a given power density. Thus, by

- 6 -

way of example only, for a conventional SMES device operating at 20 kV, a similarly powered SMES device according to the invention can operate at about 150 kV resulting in a reduction of the current of about 7.5 times.

5 Since the magnetic force in the cable is proportional to current \times magnetic flux density (B), the magnetic force is effectively reduced about 7.5 times. Furthermore, the amount of semiconductor saved will, in this example, amount to approximately 7.5 times. Similarly, the cooling losses

10 will be essentially reduced. All these factors improve the economic attractiveness of the SMES device.

A further advantage with an SMES device operating at high voltages is that charging and discharging can be rapid. It is normally very time-consuming to charge, at least

15 larger SMES devices, and by being able to connect the SMES device to a high voltage the charging time can be substantially reduced. Also the power that can be delivered from the SMES device is increased by increasing the voltage over the SMES device.

Another advantage is that an SMES device can be installed close to a large power generating unit, such as a nuclear power station. At a rapid close-down of a nuclear power station, there are great strains on the network. These can be effectively smoothed by a high voltage SMES

20 device that is able to inject the corresponding power into the system and then allow for a slow ramp down of the power.

25

Another advantage of a high voltage SMES device is that there is no need for a transformer to be provided for transforming power to and from the SMES device. The SMES

30 device can be directly coupled to a transmission or distribution network without intermediate step-up transformers. The elimination of transformers in the system leads to higher efficiency of the system. The performance of the SMES system will be greatly improved by being able to

35 connect the SMES device directly to a power network and by

- 7 -

- the increased efficiency that is created by the reduction of the number of components in the system.

Another advantage is that the SMES device is wholly electrically insulated in such a way that there is no electric field outside the superconducting cable. This facilitates the design of the mechanical structure holding the cables. It is possible to scale up the SMES device with less problems with the mechanical stability of the SMES device.

Another advantage of an SMES device with high voltage insulation is that discharges that normally occur in the electric system are prevented by the insulation system and the risk for bubble formation in the cooling medium is therefore reduced.

By connecting the coil directly to a high voltage dc source, e.g. to a high voltage ac-dc converter, charging and discharging of the coil is simplified. In particular, in an ac power transmission system, the need to transform the ac voltage down prior to connection to an ac-dc converter is eliminated. By holding the semiconducting outer layer at a controlled electric potential, e.g. ground or earth potential along its length, e.g. at spaced apart intervals along its length, the electric field generated by the superconducting means is contained within the electrical insulation.

Conveniently the coil and switch means are enclosed within a cryostat for maintaining the temperature of the superconducting means below its critical temperature (T_c). Alternatively, or in addition, the superconducting means may be internally cooled by a cryogenic fluid, e.g. liquid nitrogen, and externally thermally insulated. For example thermal insulation may conveniently be provided between the superconducting means and the surrounding electrical insulation. In some cases the electrical insulation can also function as thermal insulation.

- 8 -

By using for the intermediate layer only materials which can be manufactured with few, if any, defects and by providing the intermediate layer with the spaced apart inner and outer layers of semiconducting material having similar thermal properties, thermal and electric loads within the insulation are reduced. In particular the insulating intermediate layer and the semiconducting inner and outer layers should have at least substantially the same coefficients of thermal expansion (α) so that defects caused by different thermal expansions when the layers are subjected to heating or cooling will not arise. Ideally the electrical insulation is of substantially unitary construction. The layers of the insulation may be in close mechanical contact but are preferably joined or united together. Preferably, for example, the radially adjacent layers will be extruded together around the superconducting means. The superconducting cable is flexible at normal ambient temperatures and thus can be bent or flexed into its desired winding shape prior to operation at cryogenic temperatures.

Conveniently the electrically insulating intermediate layer comprises solid thermoplastics material, such as low or high density polyethylene (LDPE or HDPE), polypropylene (PP), polybutylene (PB), polymethylpentene (PMP), ethylene (ethyl) acrylate copolymer, cross-linked materials, such as cross-linked polyethylene (XLPE), or rubber insulation, such as ethylene propylene rubber (EPR) or silicone rubber. The semiconducting inner and outer layers may comprise similar material to the intermediate layer but with conducting particles, such as carbon black, soot or metallic particles, embedded therein. Generally it has been found that a particular insulating material, such as EPR, has similar mechanical properties when containing no, or some, carbon particles.

The screens of semiconducting inner and outer layers form substantially equipotential surfaces on the inside and outside of the insulating intermediate layer so that the

- 9 -

electric field, in the case of concentric semiconducting and insulating layers, is substantially radial and confined within the intermediate layer. In particular, the semiconducting inner layer is arranged to be in electrical contact with, and to be at the same potential as, the superconducting means which it surrounds. The semiconducting outer layer is designed to act as a screen to prevent losses caused by induced voltages. Induced voltages could be reduced by increasing the resistance of the outer layer. Since the thickness of the semiconducting layer cannot be reduced below a certain minimum thickness, the resistance can only be reduced by selecting a material for the layer having a higher resistivity. However, if the resistivity of the semiconducting outer layer is too great the voltage potential between adjacent spaced apart points at a controlled, e.g. earth, potential will become sufficiently high as to risk the occurrence of corona discharge with consequent erosion of the insulating and semiconducting layers. The semiconducting outer layer is therefore a compromise between a conductor having low resistance and high induced voltage losses but which is easily connected to a controlled electric potential, typically earth or ground potential, and an insulator which has high resistance with low induced voltage losses but which needs to be connected to the controlled electric potential along its length. Thus the resistivity ρ_s of the semiconducting outer layer should be within the range $\rho_{\min} < \rho_s < \rho_{\max}$, where ρ_{\min} is determined by permissible power loss caused by eddy current losses and resistive losses caused by voltages induced by magnetic flux and ρ_{\max} is determined by the requirement for no corona or glow discharge.

If the semiconducting outer layer is earthed, or connected to some other controlled electric potential, at spaced apart intervals along its length, there is no need for an outer metal shield and protective sheath to surround the semiconducting outer layer. The diameter of the cable is thus reduced allowing more turns to be provided for a given size of winding.

- 10 -

The electrical insulation can be extruded over the superconducting means or a lapped concept can be used. This can include both the semiconducting layers and the electrically insulating layer. An insulation can be made of
5 an all-synthetic film with inner and outer semiconducting layers made of polymeric thin film of, for example, PP, PET, LDPE or HDPE with embedded conducting particles, such as carbon black or metallic particles.

For the lapped concept a sufficiently thin film will
10 have butt gaps smaller than the so-called Paschen minima, thus rendering liquid impregnation unnecessary. A dry, wound multilayer thin film insulation has also good thermal properties and can be combined with a superconducting pipe as an electric conductor and have coolant, such as liquid
15 nitrogen, pumped through the pipe.

Another example of electrical insulation is similar to a conventional cellulose based cable, where a thin cellulose based or synthetic paper or non-woven material is lap wound around a conductor. In this case the semi-
20 conducting layers can be made of cellulose paper or non-woven material made from fibres of insulating material and with conducting particles embedded. The insulating layer can be made from the same base material or another material can be used.

Another example is obtained by combining film and fibrous insulating material, either as a laminate or as co-lapped. An example of this insulation system is the commercially available so-called paper polypropylene laminate, PPLP, but several other combinations of film and
30 fibrous parts are possible. In these systems various impregnations such as mineral oil or liquid nitrogen can be used.

The superconducting means may comprise low temperature semiconductors, but most preferably comprises
35 high-temperature superconducting (HTS) materials, for

- 11 -

example HTS wires or tape helically wound on an inner tube. The HTS tape conveniently comprises silver-sheathed BSCCO-2212 or BSCCO-2223 (where the numerals indicate the number of atoms of each element in the $[\text{Bi}, \text{Pb}]_2 \text{Sr}_2 \text{Ca}_2 \text{Cu}_3 \text{O}_x$ molecule) and hereinafter such HTS tapes will be referred to as "BSCCO tape(s)". BSCCO tapes are made by encasing fine filaments of the oxide superconductor in a silver or silver oxide matrix by a powder-in-tube (PIT) draw, roll, sinter and roll process. Alternatively the tapes may be formed by a surface coating process. In either case the oxide is melted and resolidified as a final process step. Other HTS tapes, such as TiBaCaCuO (TBCCO-1223) and YBaCuO (YBCO-123) have been made by various surface coating or surface deposition techniques. Ideally an HTS wire should have a current density beyond $j_c \sim 10^5 \text{ Acm}^{-2}$ at operation temperatures from 65 K, but preferably above 77 K. The filling factor of HTS in the matrix needs to be high so that the engineering current density $j_e > 10^4 \text{ Acm}^{-2}$. j_c should not drastically decrease with applied field within the Tesla range. The helically wound HTS tape is cooled to below the critical temperature T_c of the HTS by a cooling fluid, preferably liquid nitrogen, passing through the inner support tube.

A cryostat layer may be arranged around the helically wound HTS tape to thermally insulate the cooled HTS tape from the electrically insulating material. Alternatively, however, the cryostat may be dispensed with. In this latter case, the electrically insulating material may be applied directly over the superconducting means. Alternatively a space may be provided between the superconducting means and the surrounding insulating material, the space either being a void space or a space filled with compressible material, such as a highly compressible foamed material. The space reduces expansion/contraction forces on the insulation system during heating from/cooling to cryogenic temperatures. If the space is filled with compressible material, the latter can be made semiconducting to ensure electrical contact between the semiconducting inner layer and the superconducting means.

- 12 -

Other designs of superconducting means are possible, the invention being directed to transformer windings, formed from superconducting cables of any suitable design having a surrounding electrical insulation of the type described above. For example other types of superconducting means may comprise, in addition to internally cooled HTS material, externally cooled HTS material or externally and internally cooled HTS material. In the latter type of HTS cable, two concentric HTS conductors separated by cryogenic insulation and cooled by liquid nitrogen are used to transmit electricity. The outer conductor acts as the return path and both HTS conductors may be formed of one or many layers of HTS tape for carrying the required current. The inner conductor may comprise HTS tape wound on a tubular support through which liquid nitrogen is passed. The outer conductor is cooled externally by liquid nitrogen and the whole assembly may be surrounded by a thermally insulating cryostat.

According to another aspect of the present invention there is provided an electric power transmission system characterised in that an SMES device according to said one aspect is connected to a high voltage source, preferably a high voltage dc source.

The SMES device may be in the form of a cable and preferably a cable with high inductance. The electrical insulation of the cable can be made of conductor tape or wire with several layers where all layers are wound in the same direction, instead of as conventionally winding the layers in opposite direction in order to compensate for the inductance. Such cable with an extruded insulation system could be directly incorporated into a transmission line, for example as one line of a bipolar dc system.

It is also possible to use such cable to build up a solenoid with high inductance.

- 13 -

The invention as herein described can also be used with conventional low-temperature superconducting materials and with coolants such as liquid helium.

It is also possible to use the invention with an ac source. The losses are larger for an ac SMES device but if the losses are acceptable for the system to be designed, the principle of the invention is applicable.

Brief Description of the Drawings

Embodiments of the invention will now be described, by way of example only, with particular reference to the accompanying drawings, in which:

Figure 1 is a circuit diagram of an SMES device according to the present invention;

Figure 2 is a schematic sectional view, on an enlarged scale, through part of one embodiment of a high-temperature superconducting cable from which the coil of the SMES device of Figure 1 is wound;

Figure 3 is a schematic sectional view, on an enlarged scale, of another embodiment of high-temperature superconducting cable from which the coil of the SMES device of Figure 1 can be wound;

Figure 4 is a schematic view of two high voltage ac networks coupled together via a high voltage dc network and incorporating an SMES device on the dc side;

Figure 5 is a schematic view of an SMES incorporated in a high voltage dc network; and

Figure 6 is a schematic view of two converter stations with voltage source converters and combined with a high voltage bipolar dc link.

- 14 -

Figure 1 shows a coil 1 having an inductance L formed of high-temperature (T_c) superconducting (HTS) cable 12 (see Figure 2) which is connected with a high dc voltage source 2, e.g. the dc side of a high voltage ac-dc converter 5 connected to an ac power transmission line. A switch 3 is connected in parallel with the high dc voltage source 2 and is operable to short-circuit the coil 1.

When the coil 1 is connected to the dc voltage source 2, a dc current I flows and charges the coil. Due to the high current density of the superconducting cable and its virtually zero resistance, energy is simply stored by closing the switch 3 and short-circuiting the coil. The energy in the coil is stored as magnetic energy having a value of $\frac{1}{2}LI^2$. The coil 1 is thus able to store electrical energy and to provide electrical power at a fast rate when required at times of peak consumption.

The superconducting cable 12 from which the coil 1 is formed comprises an inner tubular support 13, e.g. of copper or a highly resistive metal, such as copper-nickel alloy, on which is helically wound elongate HTS material, for example BSCCO tape or the like, to form a superconducting layer 14 around the tubular support 13. A cryostat 15, arranged outside the superconducting layer, comprises two spaced apart flexible corrugated metal tubes 16 and 17. The space between the tubes 16 and 17 is maintained under vacuum and contains thermal superinsulation 18. Liquid nitrogen, or other cooling fluid, is passed along the tubular support 13 to cool the surrounding superconducting layer 14 to below its critical superconducting temperature T_c . The tubular support 13, superconducting layer 14 and cryostat 15 together constitute superconducting means of the cable 12.

Solid electrical insulation, e.g. of plastics material, is arranged outside the superconducting means. The electrical insulation comprises an inner semiconducting layer 20, an outer semiconducting layer 21 and, sandwiched between these semiconducting layers, an insulating layer 22.

- 15 -

The layers 20-22 preferably comprise thermoplastics materials providing a substantially unitary construction. The layers may be in close mechanical contact with each other but are preferably solidly connected to each other at their interfaces. Conveniently these thermoplastics materials have similar coefficients of thermal expansion and are preferably extruded together around the inner superconducting means. The electrical insulation conveniently has an electric field stress of no more than 0.2 kV/mm.

By way of example only, the solid insulating layer 22 may comprise cross-linked polyethylene (XLPE). Alternatively, however, the solid insulating layer may comprise other cross-linked materials, low density polyethylene (LDPE), high density polyethylene (HDPE), polypropylene (PP), polymethylpentene (PMP), ethylene (ethyl) acrylate copolymer, or rubber insulation, such as ethylene propylene rubber (EPR), ethylene-propylene-diene monomer (EPDM) or silicone rubber. The semiconducting material of the inner and outer layers 20 and 21 may comprise, for example, a base polymer of the same material as the solid insulating layer 22 and highly electrically conductive particles, e.g. particles of carbon black or metallic particles, embedded in the base polymer. The volume resistivity of these semiconducting layers, typically about 20 ohm·cm, may be adjusted as required by varying the type and proportion of carbon black added to the base polymer. The following gives an example of the way in which resistivity can be varied using different types and quantities of carbon black.

- 16 -

<u>Base Polymer</u>	<u>Carbon Black Type</u>	<u>Carbon Black Quantity (%)</u>	<u>Volume Resistivity $\Omega \cdot \text{cm}$</u>
Ethylene vinyl acetate copolymer/ nitrite rubber	EC carbon black	-15	350-400
- "	P-carbon black	-37	70-10
- "	Extra conducting carbon black, type I	-35	40-50
- "	Extra conducting black, type II	-33	30-60
Butyl grafted polyethylene	- "	-25	7-10
Ethylene butyl acrylate copolymer	Acetylene carbon black	-35	40-50
- "	P carbon black	-38	5-10
Ethylene propene rubber	Extra conducting carbon black	-35	200-400

The outer semiconductive layer 21 is connected to a desired controlled electric potential, e.g. earth potential, at spaced apart regions along its length, the specific spacing apart of adjacent controlled potential or earthing points being dependent on the resistivity of the layer 21.

The semiconducting layer 21 acts as a static shield and by controlling the electric potential of the outer layer, e.g. to earth potential, it is ensured that the electric field of the superconducting cable is retained within the solid insulation between the semiconducting layers 20 and 21. Losses caused by induced voltages in the layer 21 are reduced by increasing the resistance of the layer 21. However, since the layer 21 must be at least of a certain minimum thickness, e.g. no less than 0.8 mm, the resistance can only be increased by selecting the material of the layer to have a relatively high resistivity. The resistivity cannot be increased too much, however, else the voltage of the layer 21 mid-way between two adjacent earthing points will be too high with the associated risk of corona discharges occurring.

- 17 -

Instead of, or in addition to, internally cryogenically cooling the HTS cable 12, the coil 1 and switch 3 may be enclosed within a cryostat 6 (shown schematically in dashed lines in Figure 1) for keeping the coil 1 at temperatures below the critical temperature of the superconducting means. In this case the thermally insulating cryostat 15 need not be included in the HTS cable described above with reference to Figure 2. Figure 3 shows a typical design of cable having no cryostat 15. In this case the electrical insulation, provided by the layers 20-22, is extruded directly over the superconducting layer 14 wound on the tubular support 13. Although not shown, an annular gap may be provided between the electric insulation and the layer 14 to cater for the differences in thermal expansion/contraction of the electrical insulation and the layer 14. This annular gap could be a void space or could be filled with compressible material, such as highly compressible foam material. If such an annular gap is provided, the semiconducting inner layer 20 is preferably placed in electrical contact with the superconducting layer 14. For example if the compressible foam material is included in the annular gap the foam material may be made semiconducting.

Figure 4 shows a high voltage system comprising two high voltage ac networks, N1 and N2, T1Y and T2Y are converter transformers in Y/Y coupling and T1D and T2D are converter transformers in Y/D coupling. SCR11, SCR12, SCR21 and SCR22 are series-connected 6-pulse line-commutated bridge-connected converters. The converters SCR11 and SCR12 are linked with the converters SCR21 and SCR22 via a dc link DCL which comprises an energy storage device in the form of a superconducting magnetic storage device SMES.

The voltage over the converters SCR11 and SCR12 is U1 and the voltage over converters SCR21 and SCR22 is U2. U1 and U2 are each controlled in a conventional manner by control equipment (not shown) connected with its respective

- 18 -

converter. The current I_d runs through the dc link DCL and the device SMES.

In the system shown in Figure 4, $U1 - U2 = L \cdot di/dt$, which means the charging and discharging of the device SMES can be controlled by the control angles of the converters. One or both converters can charge or discharge the SMES. By controlling $U1=U2$, the content of energy of the SMES can be unaffected.

Figure 5 shows the same basic high voltage system as Figure 4. In Figure 5, however, the superconducting magnetic energy storage device SMES is used as a storage device for the ac network N1 and is charged via the converters SCR11 and SCR12, with switch S1 closed and switch S2 open. During charging of the device SMES, the current through the coil can be measured and charging continues until a nominal value is reached. When the SMES is fully charged, S1 opens and S2 closes. For feeding the network N1, for example in the case of a power loss on the network, S1 closes and S2 is opened.

In the Figure 5 system, the superconducting magnetic energy storage device SMES is part of a high voltage dc transmission system with a dc link. A pole control device, PCM, is needed when providing the network N2 with power.

Figure 6 shows a high voltage system having two voltage-controlled converters VSC1 and VSC2, which are connected via a dc link in the form of a double cable TC. The dc link is bipolar in that the capacitors C11 and C12 and the capacitors C21 and C22 are respectively connected to ground at their connecting point. A superconducting magnetic energy storage device SMES is arranged at one pole of the converter VSC1. It is also possible to arrange the superconducting magnetic energy storage device in the form of a cable as one part of the bipolar dc link.

- 19 -

Although the invention has been described with specific reference to an SMES device having a coil for connection in series with a dc voltage source, the invention is also intended to embrace connection of the coil to an ac
5 voltage source.

The term "high voltage" used in this specification is intended to mean up to 800 kV or even higher. An SMES device may be connected to such high voltage networks and at high powers of up to 1000 MVA. At high voltages, partial
10 discharges, or PD, constitute a serious problem for known insulation systems. If cavities or pores are present in the insulation, internal corona discharges may arise whereby the insulating material is gradually degraded eventually leading to breakdown of the insulation. The electric load on the
15 electrical insulation of the superconducting means of an SMES device according to the present invention is reduced by ensuring that the inner portion of the electrical insulation is at substantially the same electric potential as the superconducting means and that the outer portion of the
20 electrical insulation is at a controlled potential. Thus the electric field is distributed substantially uniformly over the thickness of the electrically insulating portion of the insulation between the inner and outer portions. By having materials for the electrical insulation with similar
25 thermal properties and with few defects in the layers or portions, the possibility of PD is reduced.

An additional advantage of the present invention is that, since the SMES device operates at high voltage, the current can be reduced for a given power density. Thus for
30 a conventional SMES device operating at 20 kV, a similarly powered SMES device according to the invention can operate at about 150 kV resulting in a reduction of the current of about 7.5 times. Since the magnetic force in the cable is proportional to current x magnetic flux density (B), the
35 magnetic force is effectively reduced about 7.5 times. Furthermore, the amount of semiconductor saved will, in this example, amount to approximately 7.5 times. Similarly, the

- 20 -

cooling losses will be essentially reduced. All these factors improve the economic attractiveness of the SMES device.

The present invention is not limited to high temperature superconductivity. Due to the high magnetic field in magnetic energy storage, low temperature superconductors are still attractive, even though they require cryostats operating between 1-15 K, depending on the type of low temperature superconductor utilised. Well known examples are based on Niobium, such as NbTi, Nb₃Sn and Nb₃Al. Other examples are V₃Ga and Nb₃Ge. The most common superconductor used is NbTi which can be utilised in magnetic field densities up to approximately 9 T at 4.2 K (or 11 T at 1.8 K). For higher field densities, NbTi cannot be used and is replaced by Nb₃Sn.

- 21 -

CLAIMS

1. An SMES device comprising a coil (1) for connection in series with a voltage source (2), e.g. a dc voltage source, and wound from a superconducting cable (12) having superconducting means (14) which, in use, is maintained at cryogenic temperatures below its critical temperature (T_c) and which is surrounded by electrical insulation (20-22), and switch means (3) for short-circuiting the coil (1), characterised in that the said electrical insulation comprises an inner layer (20) of semiconducting material electrically connected to said superconducting means, an outer layer (21) of semiconducting material at a controlled electric potential along its length and an intermediate layer (22) of solid electrically insulating material positioned between said inner and outer layers (20 and 21).

2. An SMES device according to claim 1, characterised in that the device further comprises a cryostat (6) in which the coil (1) and switch means (3) are enclosed.

3. An SMES device according to claim 1 or 2, characterised in that said superconducting means comprises high-temperature superconducting (HTS) means.

4. An SMES device according to claim 3, characterised in that said high-temperature superconducting (HTS) means comprises at least one layer (14) of high-temperature superconducting (HTS) material, cooling means (13) for cryogenically cooling the layer(s) (14) of HTS material below the critical temperature (T_c) of the HTS material and thermally insulating means (15) surrounding the layer(s) (14) of HTS material and the cooling means (13).

5. An SMES device according to claim 4, characterised in that the cooling means (13) comprises a

- 22 -

support tube (13) through which cryogenic cooling fluid is passed and in that the at least one layer (14) of HTS material comprises HTS tape or conductors wound in a helical layer on said support tube (13).

5 6. An SMES device according to claim 4 or 5, characterised in that the thermally insulating means (15) comprises an annular space under vacuum and containing thermal insulation (18).

10 7. An SMES device according to any one of the preceding claims, characterised in that the semiconducting outer layer (21) has a resistivity of from 1 to 1000 ohm·cm.

15 8. An SMES device according to claim 6, characterised in that the said outer layer (21) has a resistivity of from 10 to 500 ohm·cm, preferably from 10 to 100 ohm·cm.

 9. An SMES device according to any one of the preceding claims, characterised in that the resistance per axial unit length of the semiconducting outer layer (21) is from 5 to 50,000 ohm.m⁻¹.

20 10. An SMES device according to any one of claims 1 to 8, characterised in that the resistance per axial unit of length of the semiconducting outer layer (21) is from 500 to 25,000 ohm.m⁻¹, preferably from 2,500 to 5,000 ohm.m⁻¹.

25 11. An SMES device according to any one of the preceding claims, characterised in that the semiconducting outer layer (21) is contacted by conductor means at said controlled electric potential at spaced apart regions along its length, adjacent contact regions being sufficiently close together that the voltages of mid-points between
30 adjacent contact regions are insufficient for corona discharges to occur within the electrically insulating means.

- 23 -

12. An SMES device according to any one of the preceding claims, characterised in that said controlled electric potential is at or close to earth potential.

13. An SMES device according to any one of the preceding claims, characterised in that the said intermediate layer (22) is in close mechanical contact with each of said inner and outer layers (20 and 21).

14. An SMES device according to any one of claims 1 to 12, characterised in that the said intermediate layer (22) is joined to each of said inner and outer layers (20 and 21).

15. An SMES device according to any one of the preceding claims, characterised in that the strength of the adhesion between the said intermediate layer (22) and each of the semiconducting inner and outer layers (20, 21) is of the same order of magnitude as the intrinsic strength of the material of the intermediate layer.

16. An SMES device according to claim 14 or 15, characterised in that the said layers (20-22) are joined together by extrusion.

17. An SMES device according to claim 16, characterised in that the inner and outer layers (20, 21) of semiconducting material and the insulating intermediate layer (22) are applied together over the superconducting means through a multi layer extrusion die.

18. An SMES device according to any one of the preceding claims, characterised in that said inner layer (20) comprises a first plastics material having first electrically conductive particles dispersed therein, said outer layer (21) comprises a second plastics material having second electrically conductive particles dispersed therein and said intermediate layer (22) comprises a third plastics material.

- 24 -

19. An SMES device according to claim 18, characterised in that each of said first, second and third plastics materials comprises an ethylene butyl acrylate copolymer rubber, an ethylene-propylene-diene monomer rubber (EPDM) or an ethylene-propylene copolymer rubber (EPR), LDPE, HDPE, PP, PB, PMB XLPE, EPR or silicone rubber.

20. An SMES device according to claim 18 or 19, characterised in that said first, second and third plastics materials have at least substantially the same coefficients of thermal expansion.

21. An SMES device according to claim 18, 19 or 20 characterised in that said first, second and third plastics materials are the same material.

22. An electric power transmission system comprising an SMES device according to any one of the preceding claims connected to a high voltage source.

23. A high voltage system comprising an SMES device, characterised in that the SMES device has superconducting conductor means which is insulated against high voltage by an electric insulation system arranged concentrically around the conductor means.

24. A high voltage system according to claim 23, characterised in that the high voltage system comprises a high voltage network and that the SMES device is directly connected to the high voltage network without an intermediate transformer.

25. A high voltage system according to claim 24, characterised in that the network is a high voltage dc network.

- 25 -

26. A high voltage system according to claim 25, characterised in that the dc network is at a voltage exceeding 10 kV.

27. A high voltage system according to claim 24, characterised in that the SMES device is coupled to a high voltage ac network via a converter.

28. A high voltage system according to claim 25, comprising several ac networks connected via the dc network and the SMES device, the dc network being connected to the ac networks so that the SMES device can provide the ac networks with power.

29. A high voltage system according to any one of claims 23 to 28, characterised in that the SMES device comprises a coil.

30. A high voltage system according to any one of claims 23 to 28, characterised in that the SMES device comprises a cable without turns.

31. A high voltage system according to claim 27 of claim 29 when dependent on claim 27, characterised in that the SMES is one part of a bipolar dc link.

32. A high voltage system according to any one of claims 23 to 31, characterised in that said insulation system is extruded around the conductor means and comprises a first integral part forming an inner layer in electric contact with the conductor means and having semiconducting properties, a second integral part forming an outer layer around the insulation and having semiconducting properties and an insulating integral third part between the first and second integral parts.

33. A high voltage system according to an one of claims 23 to 31, characterised in that said insulation system comprises an all-synthetic film wound in overlapping

- 26 -

layers around the conductor means with an inner part in electric contact with the conductor means and having semiconducting properties, an electrically insulating intermediate part and an outer part surrounding the intermediate part and having semiconducting properties.

34. A high voltage system according to any of claims 23 to 31, characterised in that said insulation system comprising one or more of a cellulose-based, synthetic paper or non-woven fibre material, co-lapped or laminated with a synthetic film and having an inner part in electric contact with the conductor means and having semiconducting properties, an electrically insulating intermediate part and an outer part around said intermediate part and having semiconducting properties.

35. A high voltage system according to claim 32, 33 or 34, characterised in that a cooling medium for cooling said superconductive conductor is arranged to flow within the conductor means.

36. A high voltage system according to claim 32, 33 or 34 characterised in that a cooling medium for cooling said superconductive conductors is arranged outside of the conductor means.

FIG. 1

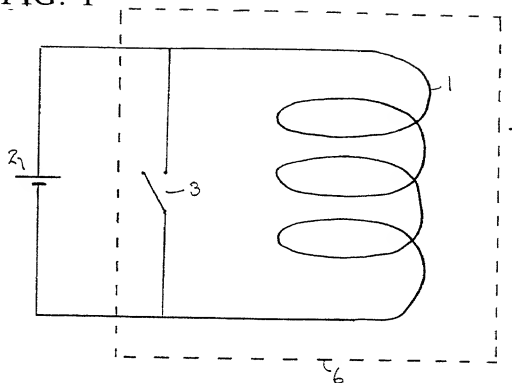


FIG. 2

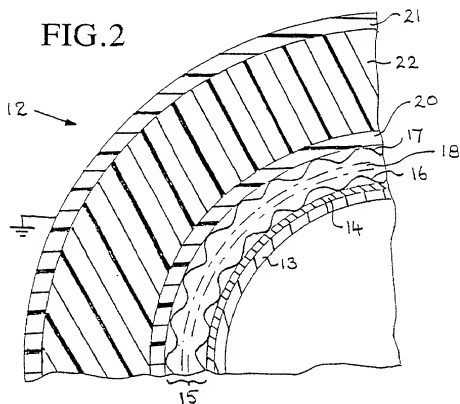


FIG. 3

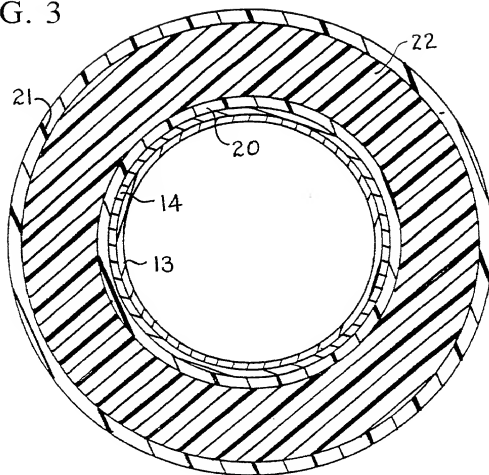


FIG. 4

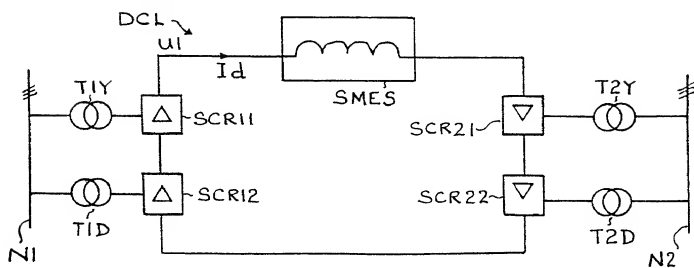
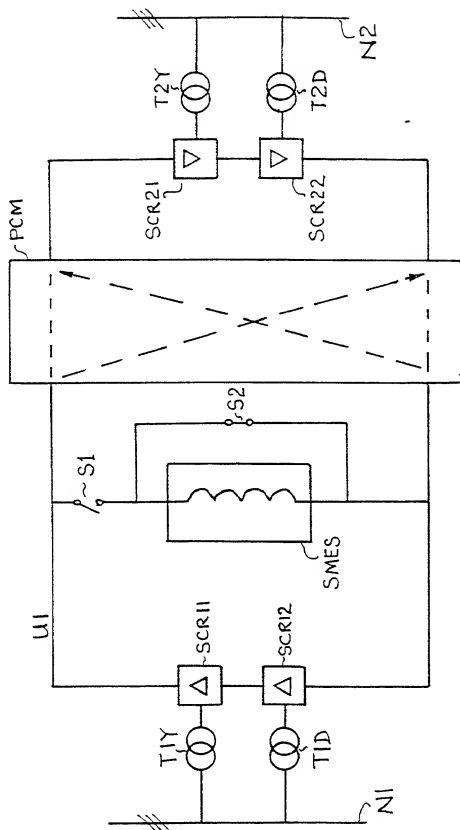


FIG. 5



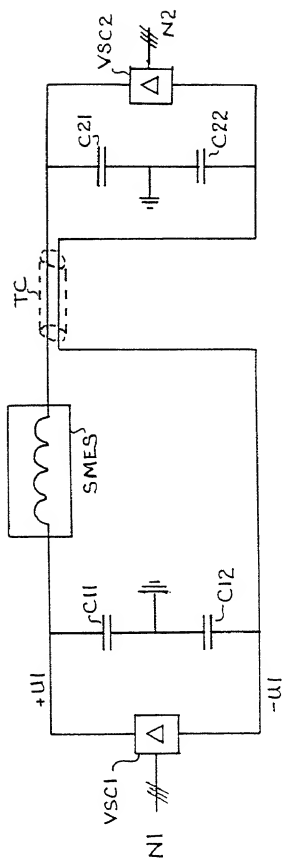


FIG. 6

Declaration, Power Of Attorney and Petition

Page 1 of 3

WE (I) the undersigned inventor(s), hereby declare(s) that:

My residence, post office address and citizenship are as stated below next to my name,

We (I) believe that we are (I am) the original, first, and joint (sole) inventor(s) of the subject matter which is claimed and for which a patent is sought on the invention entitled

MAGNETIC ENERGY STORAGE

the specification of which

☐ is attached hereto.

☒ was filed on MAY 22, 2000 as

Application Serial No. _____

and amended on _____.

☒ was filed as PCT international application

Number PCT/EP98/07740

on 30 NOVEMBER 1998,

and was amended under PCT Article 19

on _____ (if applicable).

We (I) hereby state that we (I) have reviewed and understand the contents of the above-identified specification, including the claims, as amended by any amendment referred to above.

We (I) acknowledge the duty to disclose information known to be material to the patentability of this application as defined in Section 1.56 of Title 37 Code of Federal Regulations.

We (I) hereby claim foreign priority benefits under 35 U.S.C. § 119(a)-(d) or § 365(b) of any foreign application(s) for patent or inventor's certificate, or § 365(a) of any PCT International application which designated at least one country other than the United States, listed below and have also identified below, by checking the box, any foreign application for patent or inventor's certificate, or PCT International application having a filing date before that of the application on which priority is claimed. Prior Foreign Application(s)

Application No.	Country	Day/Month/Year	Priority Claimed
<u>9725318.1</u>	<u>GREAT BRITAIN</u>	<u>28 NOVEMBER 1997</u>	<input checked="" type="checkbox"/> Yes <input type="checkbox"/> No
_____	_____	_____	<input type="checkbox"/> Yes <input type="checkbox"/> No
_____	_____	_____	<input type="checkbox"/> Yes <input type="checkbox"/> No
_____	_____	_____	<input type="checkbox"/> Yes <input type="checkbox"/> No

We (I) hereby claim the benefit under Title 35, United States Code, § 119(e) of any United States provisional application(s) listed below.

(Application Number)

(Filing Date)

(Application Number)

(Filing Date)

We (I) hereby claim the benefit under 35 U.S.C. § 120 of any United States application(s), or § 365(c) of any PCT International application designating the United States, listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States or PCT International application in the manner provided by the first paragraph of 35 U.S.C. § 112, I acknowledge the duty to disclose information which is material to patentability as defined in 37 CFR § 1.56 which became available between the filing date of the prior application and the national or PCT International filing date of this application.

Application Serial No.

Filing Date

Status (pending, patented,
abandoned)

PCT/EP98/07740

30 NOVEMBER 1998

And we (I) hereby appoint: Norman F. Oblon, Reg. No. 24,618; Marvin J. Spivak, Reg. No. 24,913; C. Irvin McClelland, Reg. No. 21,124; Gregory J. Maier, Reg. No. 25,599; Arthur I. Neustadt, Reg. No. 24,854; Richard D. Kelly, Reg. No. 27,752; James D. Hamilton, Reg. No. 28,421; Eckhard H. Kuesters, Reg. No. 28,870; Robert T. Pous, Reg. No. 29,099; Charles L. Gholz, Reg. No. 26,395; William E. Beaumont, Reg. No. 30,996; Jean-Paul Lavalleye, Reg. No. 31,451; Stephen G. Baxter, Reg. No. 32,884; Richard L. Treanor, Reg. No. 36,379; Steven P. Weihrouch, Reg. No. 32,829; John T. Goolkasian, Reg. No. 26,142; Richard L. Chinn, Reg. No. 34,305; Steven E. Lipman, Reg. No. 30,011; Carl E. Schlier, Reg. No. 34,426; James J. Kulbaski, Reg. No. 34,648; Richard A. Neifeld, Reg. No. 35,299; J. Derek Mason, Reg. No. 35,270; Surinder Sachar, Reg. No. 34,423; Christina M. Gadiano, Reg. No. 37,628; Jeffrey B. McIntyre, Reg. No. 36,867; William T. Enos, Reg. No. 33,128; Michael E. McCabe, Jr., Reg. No. 37,182; Bradley D. Lytle, Reg. No. 40,073; and Michael R. Casey, Reg. No. 40,294; our (my) attorneys, with full powers of substitution and revocation, to prosecute this application and to transact all business in the Patent Office connected therewith; and we (I) hereby request that all correspondence regarding this application be sent to the firm of OBLON, SPIVAK, McCLELLAND, MAIER & NEUSTADT, P.C., whose Post Office Address is: Fourth Floor, 1755 Jefferson Davis Highway, Arlington, Virginia 22202.

We (I) declare that all statements made herein of our (my) own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

Par HOLMBERG

NAME OF FIRST SOLE INVENTOR

Residence: Haga Parkgata 6C, S-723 36

Vasteras, Sweden

Citizen of: Sweden

Post Office Address: same as above

Signature of Inventor

Date

2-10 Udo FROMM

NAME OF SECOND JOINT INVENTOR

✓ Udo Fromm

Signature of Inventor

✓ 2000-07-14

Date

2-10 Christian SASSE

NAME OF THIRD JOINT INVENTOR

✓ Christian Sasse

Signature of Inventor

✓ 2000-07-10

Date

NAME OF FOURTH JOINT INVENTOR

Signature of Inventor

Date

NAME OF FIFTH JOINT INVENTOR

Signature of Inventor

Date

Residence: Liegatan 33, S-724 67

Vasteras, Sweden SE X

Citizen of: Denmark

Post Office Address: same as above

Residence: Drottninggatan 4B S-724 64

Vasteras, Sweden SE X

Citizen of: Germany

Post Office Address: same as above

Residence:

Citizen of:

Post Office Address:

Residence:

Citizen of:

Post Office Address: